Full 3D Simulations of BNL Silicon 3D Detectors and Comparisons with other Types of 3D Detectors

Tanja Palviainen^{1,2} and Zheng Li¹

¹Brookhaven National Laboratory ²Lappeenranta University of Technology

Work based on the period 2/15/-4/15/07 at Brookhaven National Laboratory

OUTLINE

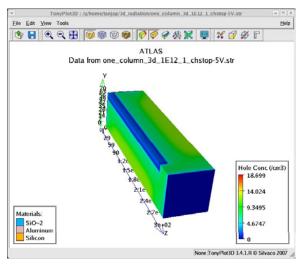
- 3D Simulation tools
- Simulated 3D detector structures
 - BNL one-sided single column
 - Comparing with Trento single column
 - BNL one-sided dual column
 - Comparing with Trento/CNM 2-sided dual column and UH dual column
- Advantages and disadvantages
- Summary

3D detector simulations

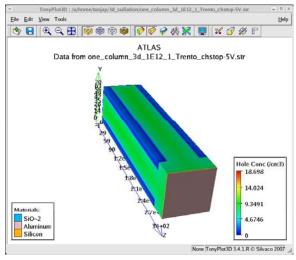
- Silicon radiation 3D detectors were simulated in three-dimensional with simulation software Silvaco
 - DEVEDIT3D
 Used to define the detector structure by defining the mesh, material regions and impurities
 - DEVICE3D (ATLAS)
 Same as S-PISCES in ATLAS 2D, the device simulation, used to solve device parameters

3D detector structures

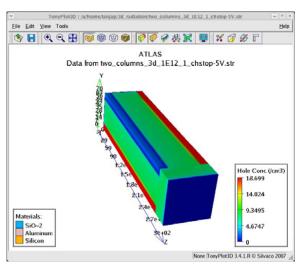
- Four different 3D detector structures were under investigation.
- In the all cases, the bulk was p-type.



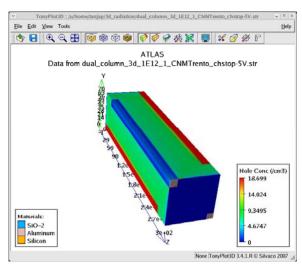
a) BNL single column



c) Trento single column

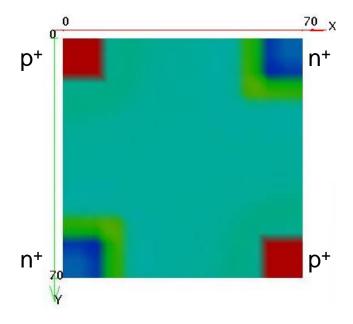


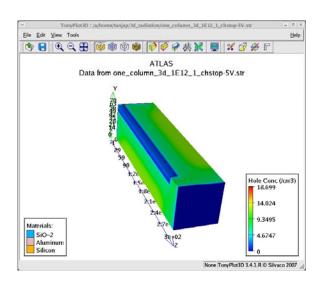
b) BNL dual column



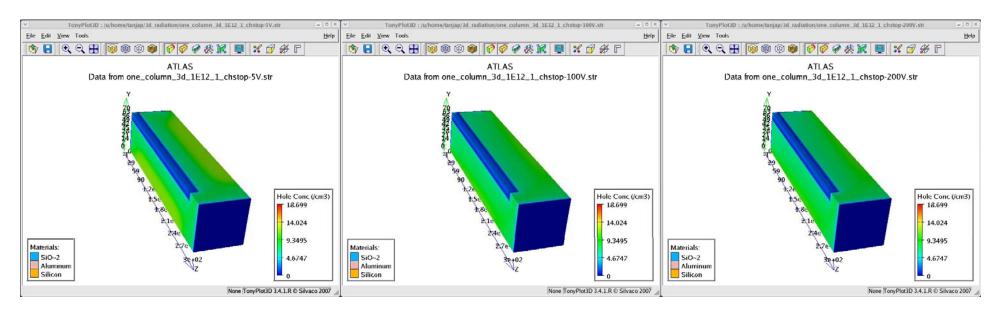
d) CNM, Trento dual column

- BNL
- One unit cell has two n-type columns (270um) on the opposite corners, and they are surrounded by p-stops
- Two other corners have p-implants (0.5um)

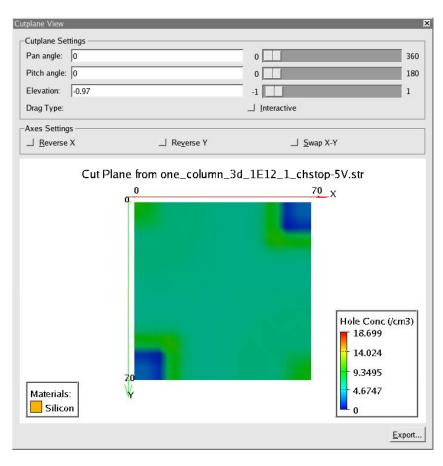


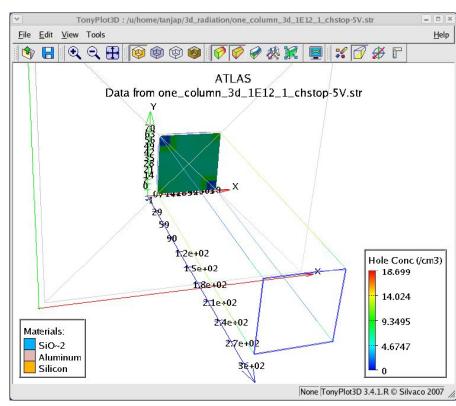


5V 100V 200V

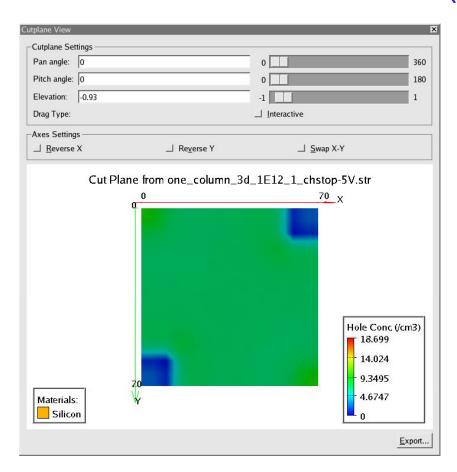


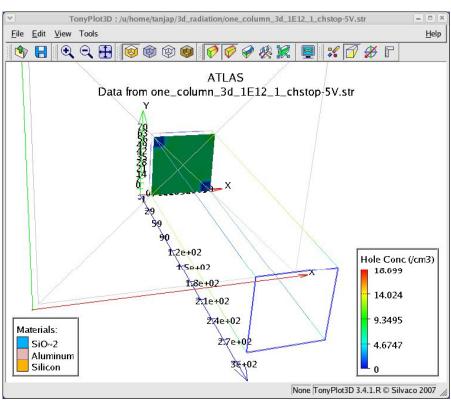
Hole concentration All fully depleted

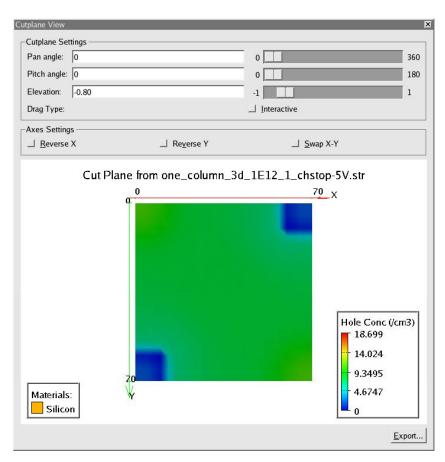


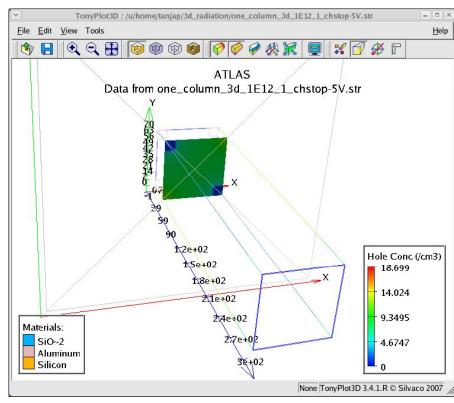


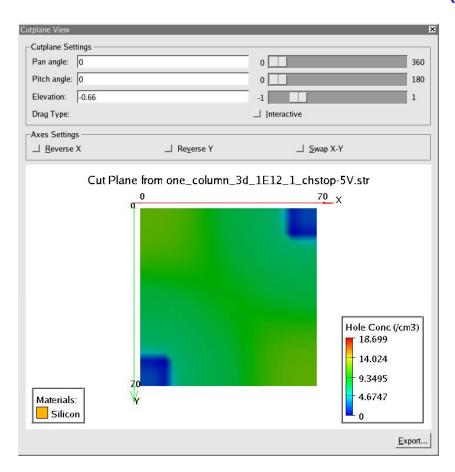
Make a ovie, insert timing Stop at the first middle and the end slides tanjap, 4/13/2007 t1

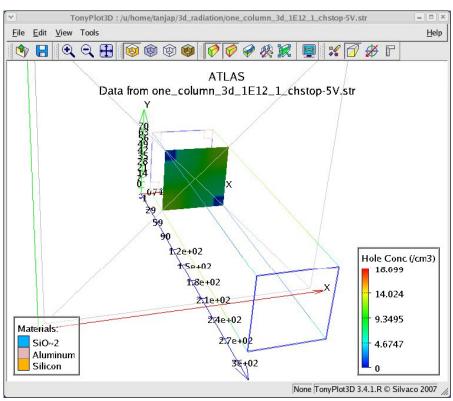


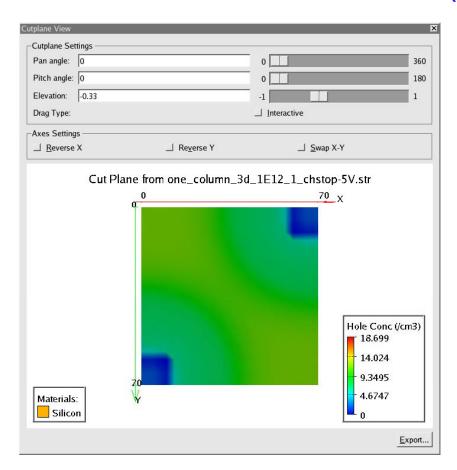


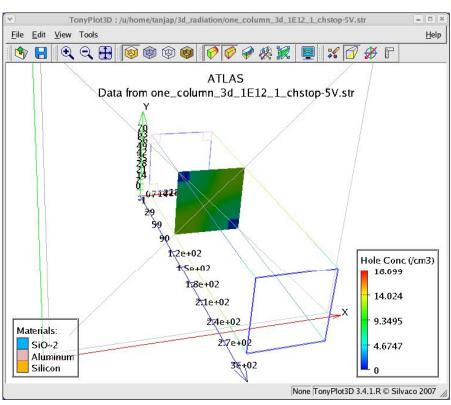


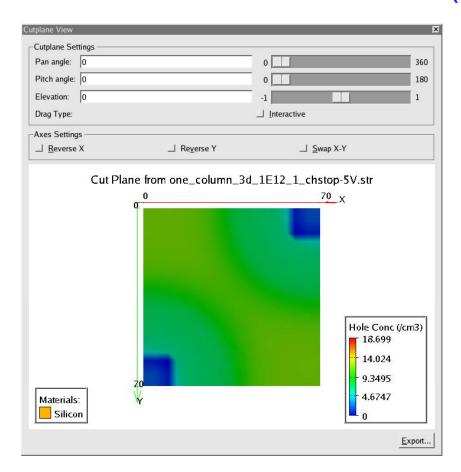


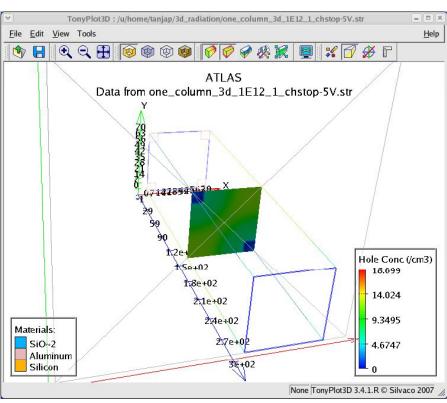


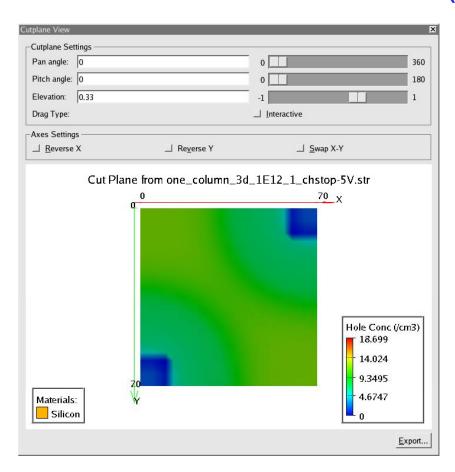


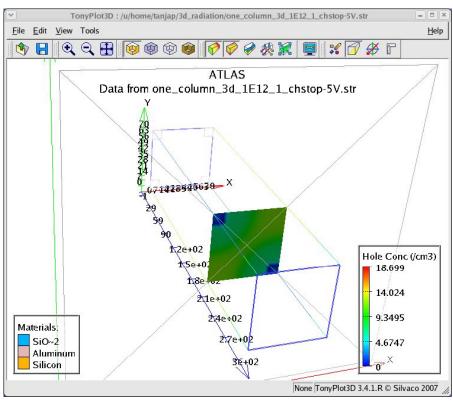


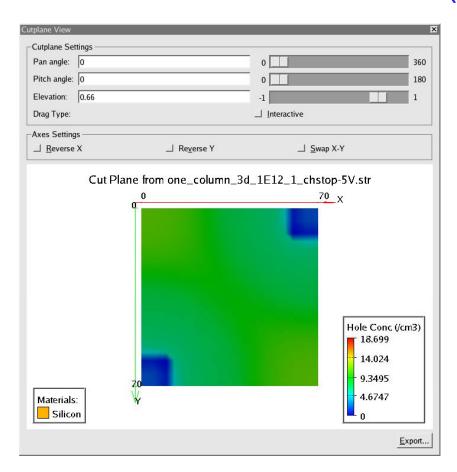


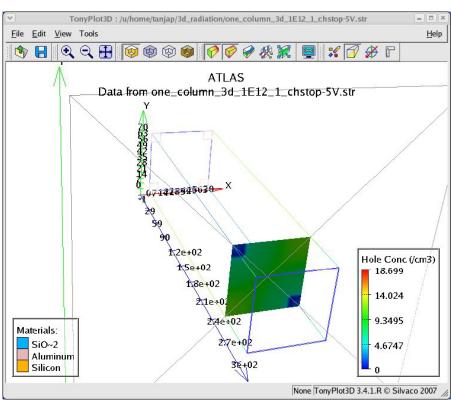


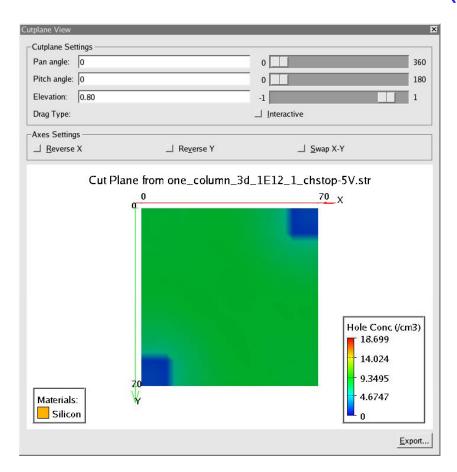


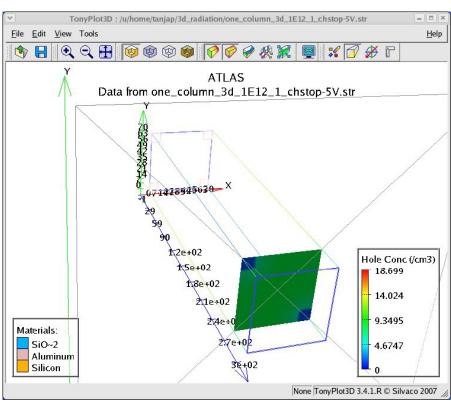


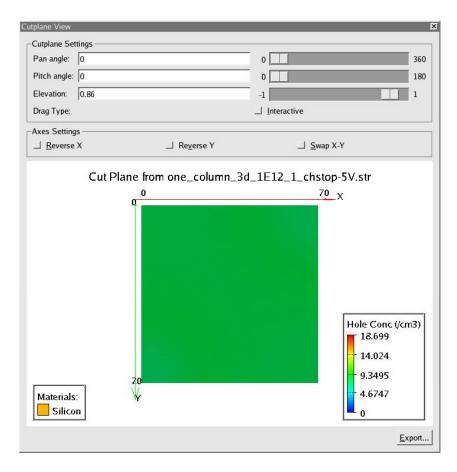


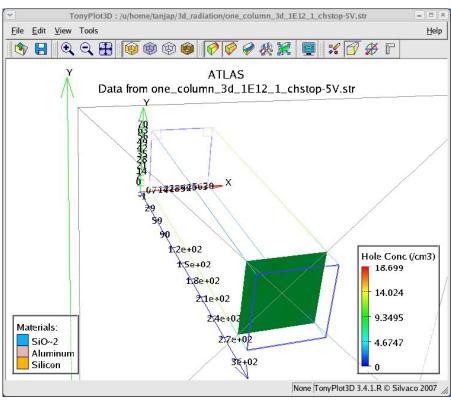


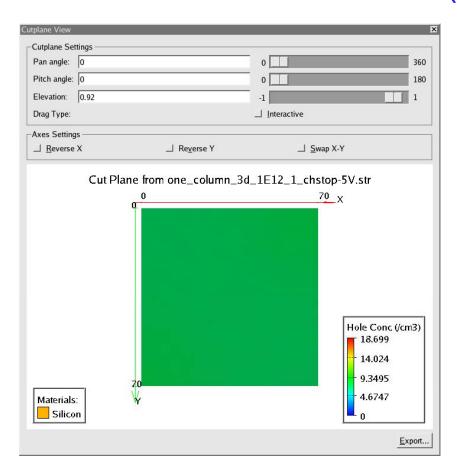


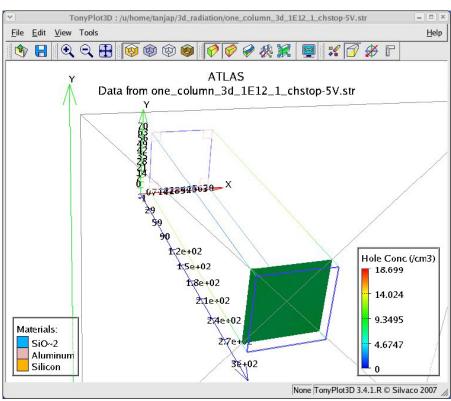


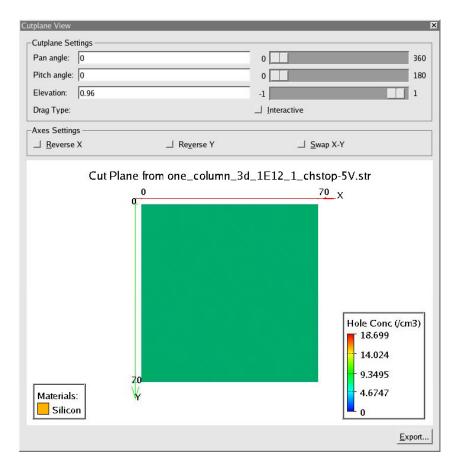


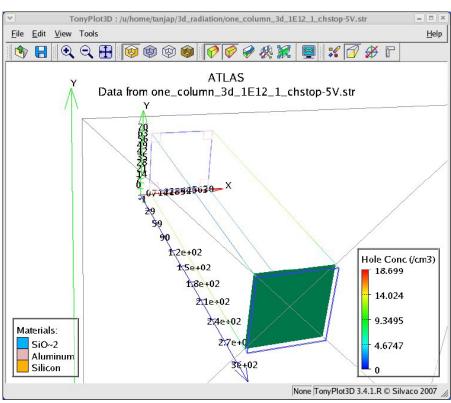




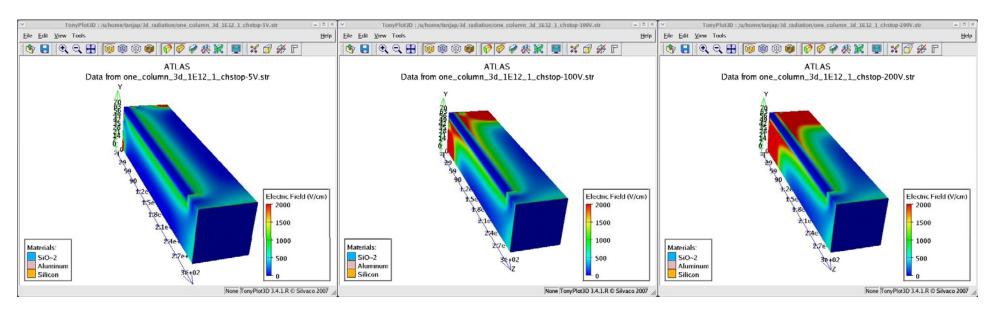


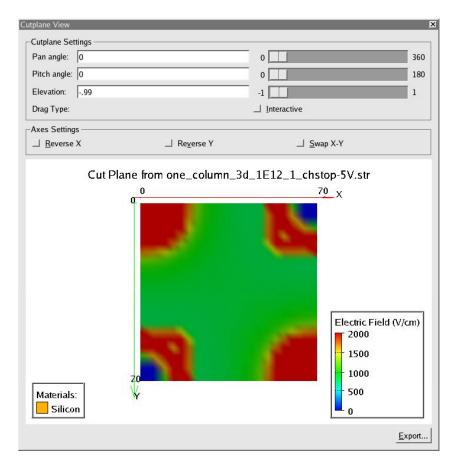


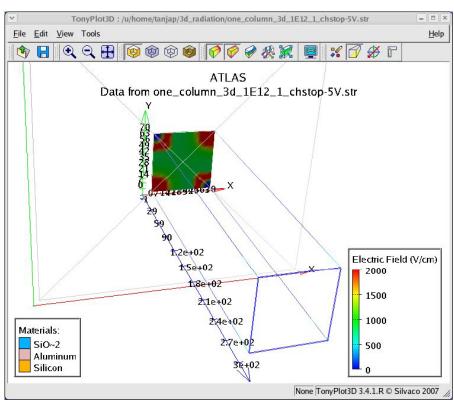


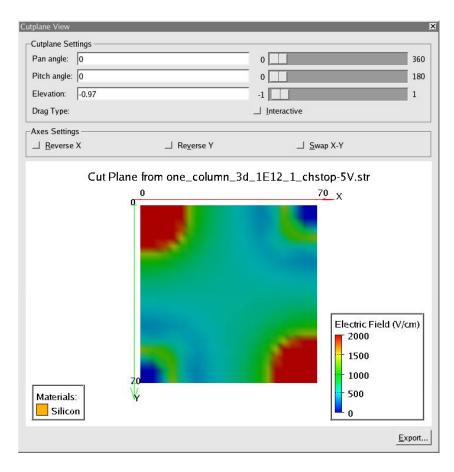


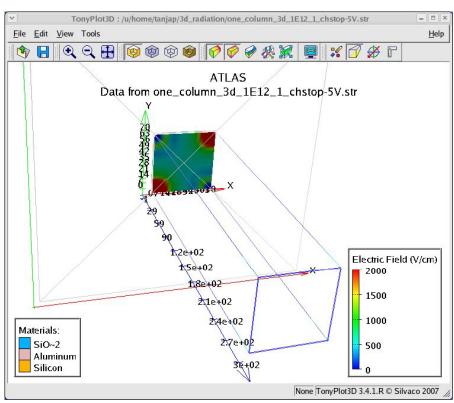
5V 100V 200V

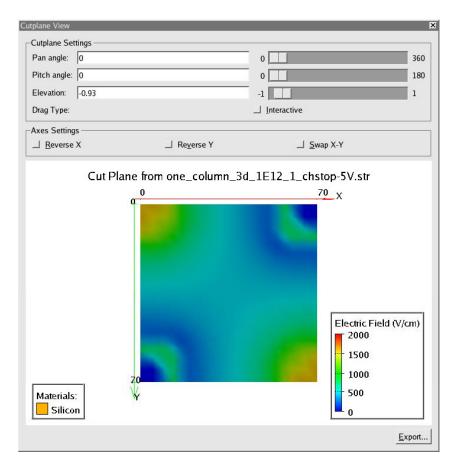


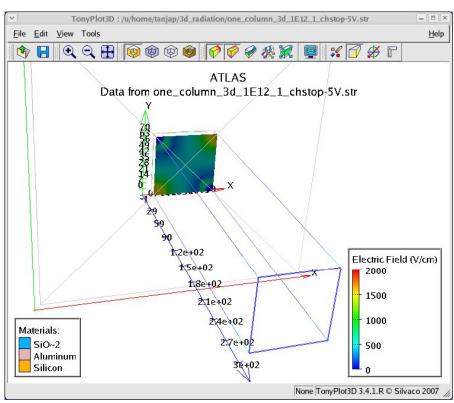


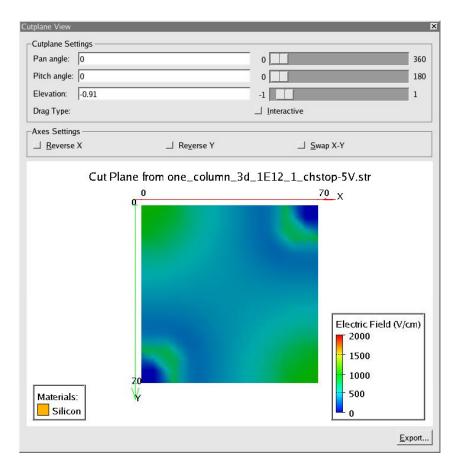


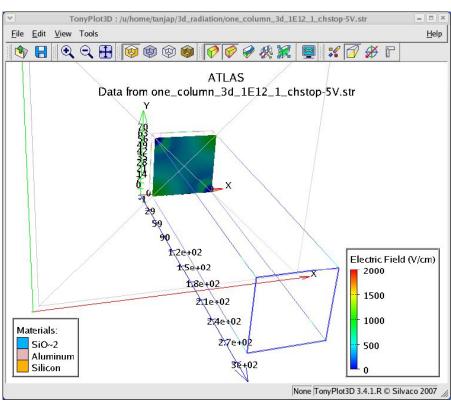


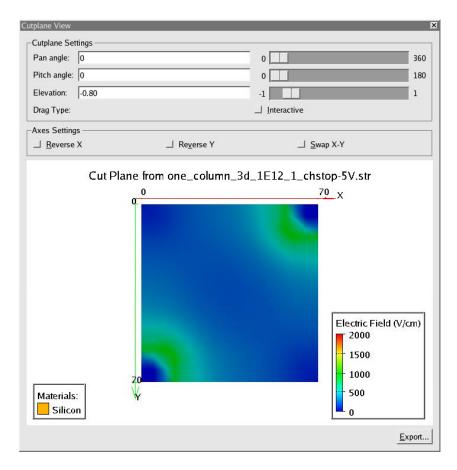


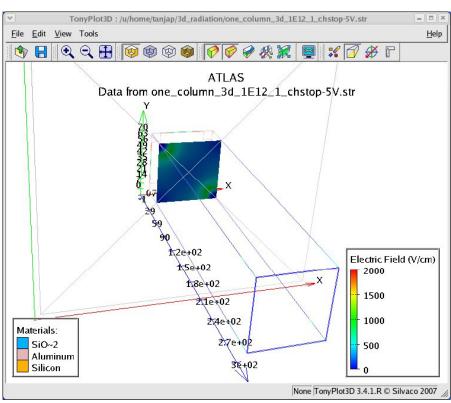


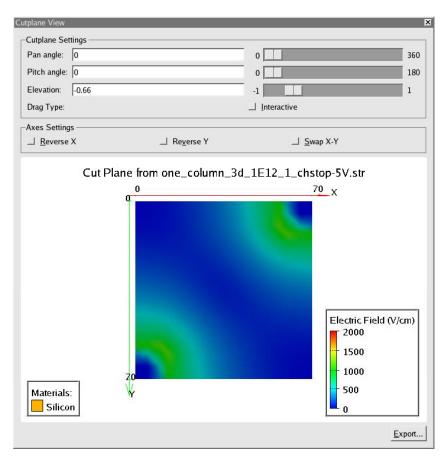


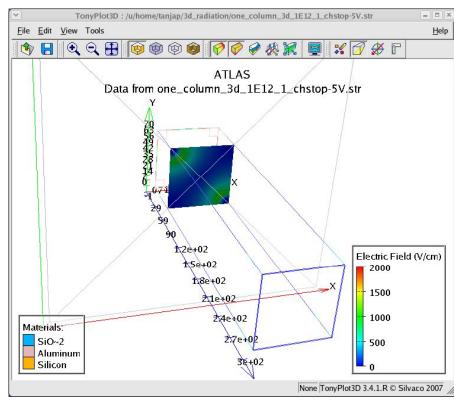


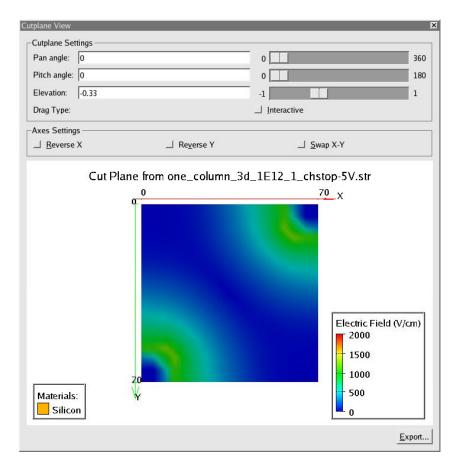


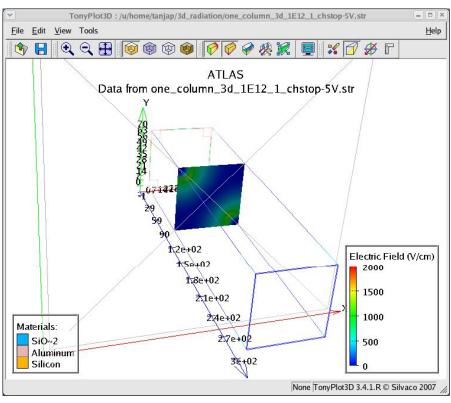


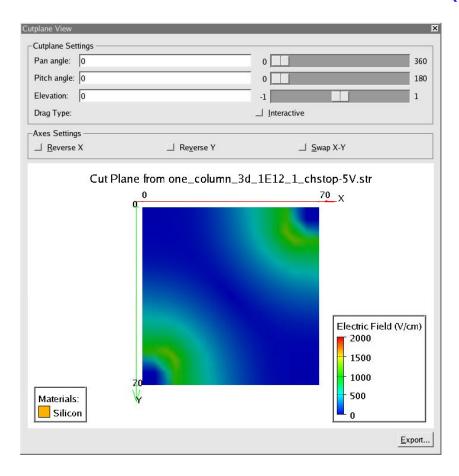


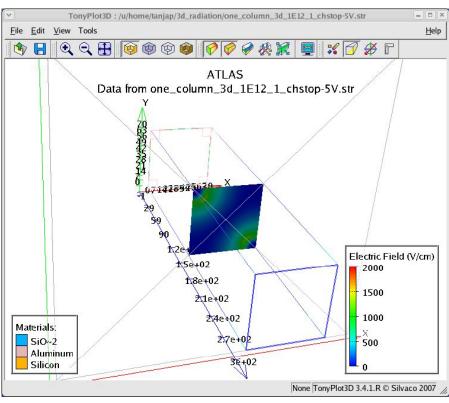


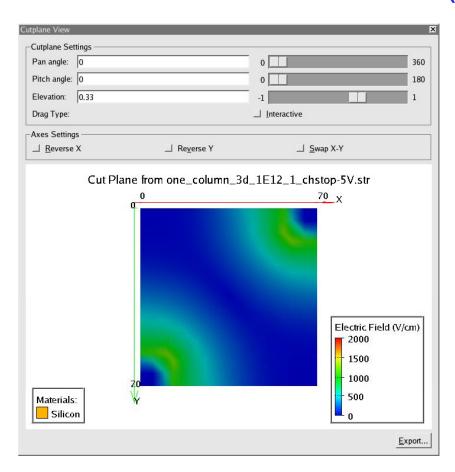


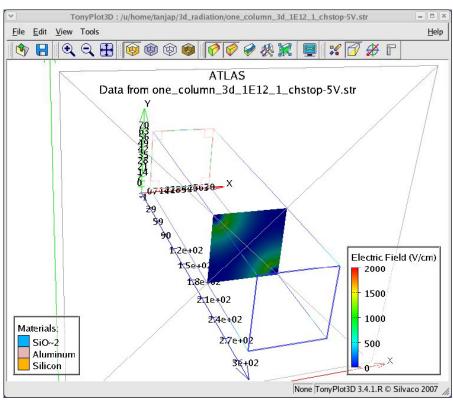


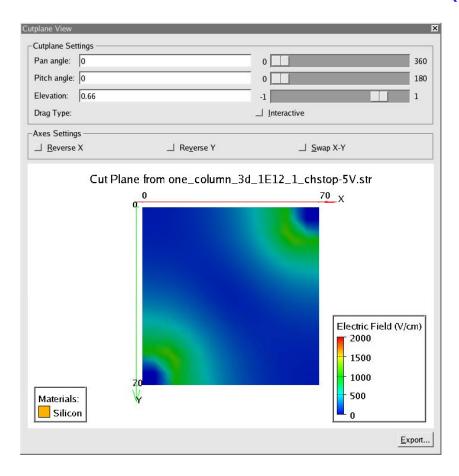


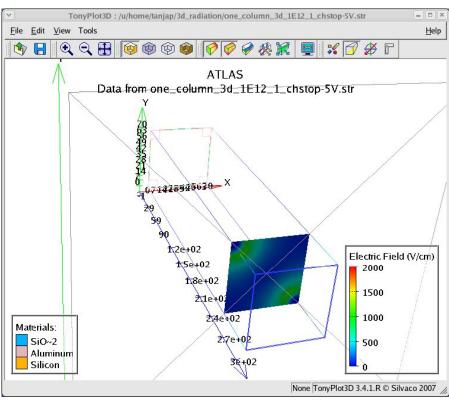


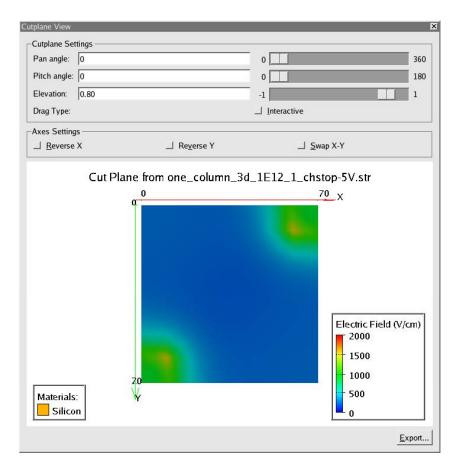


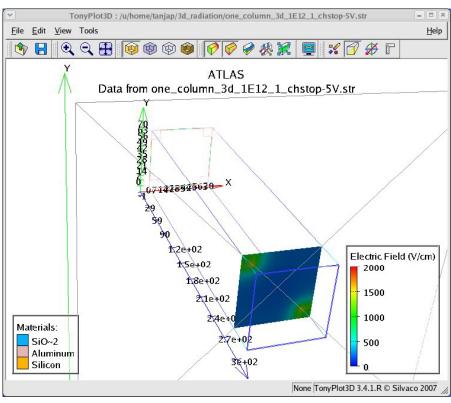


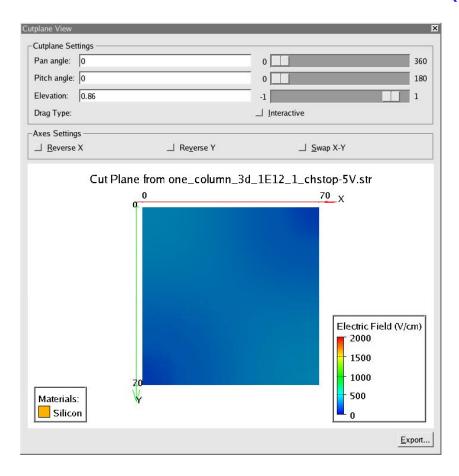


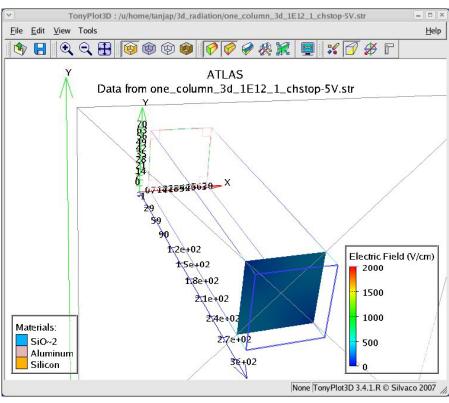


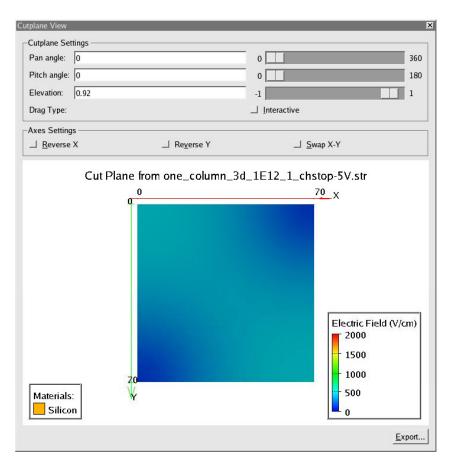


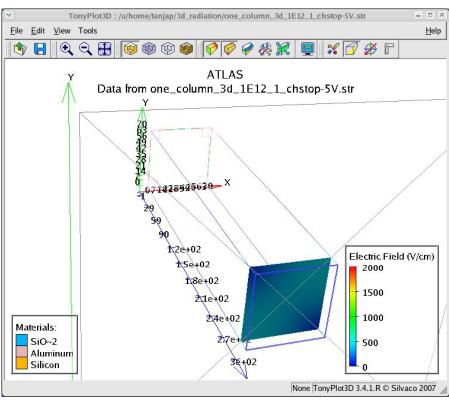


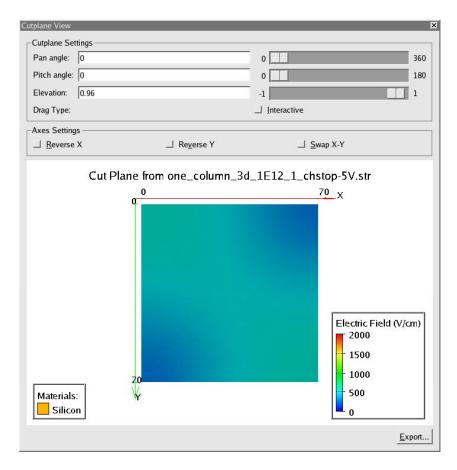


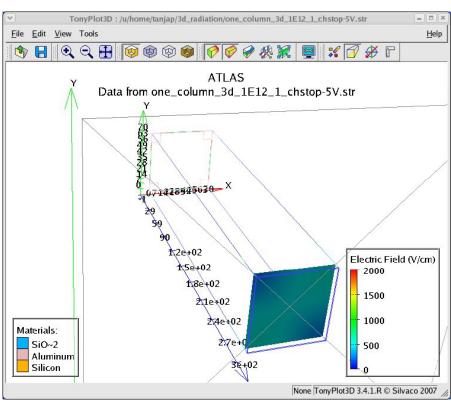


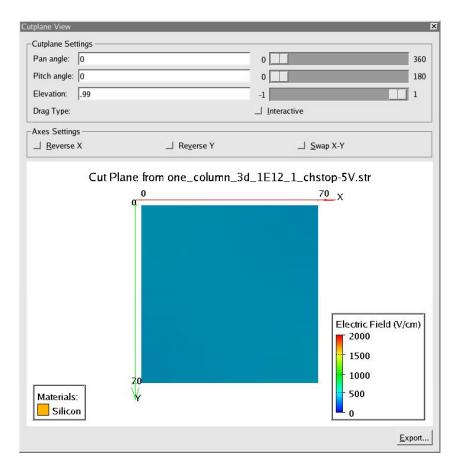


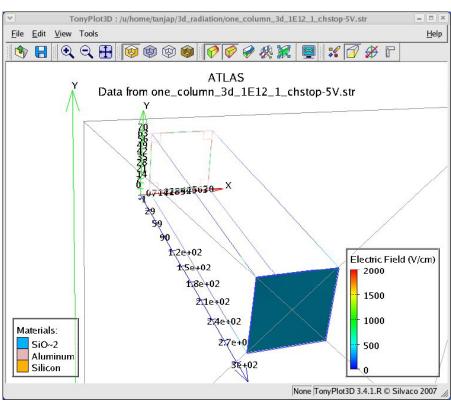


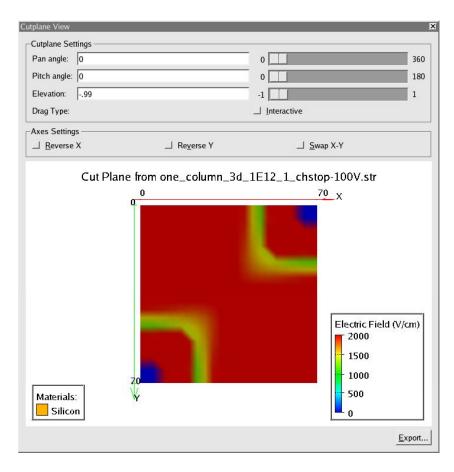


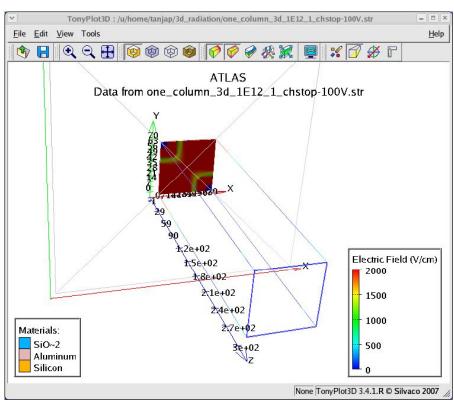


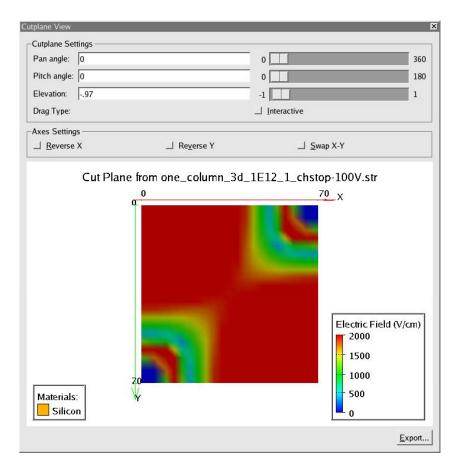


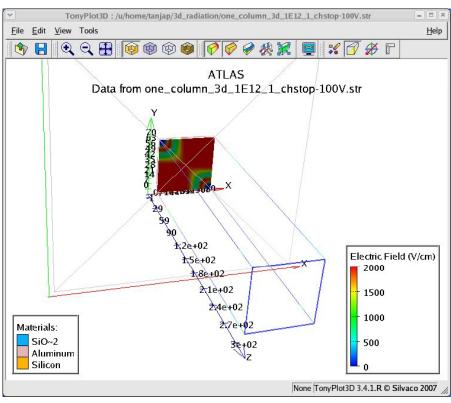


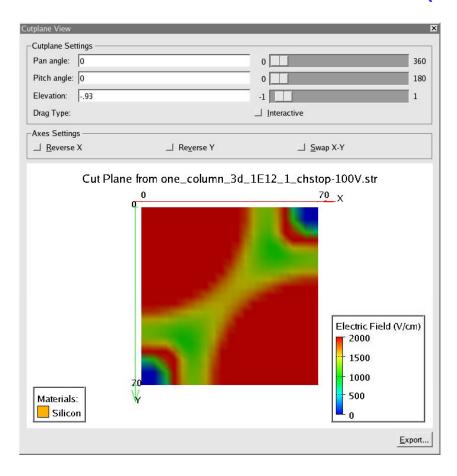


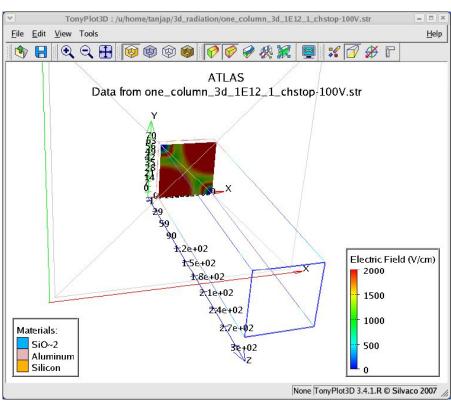


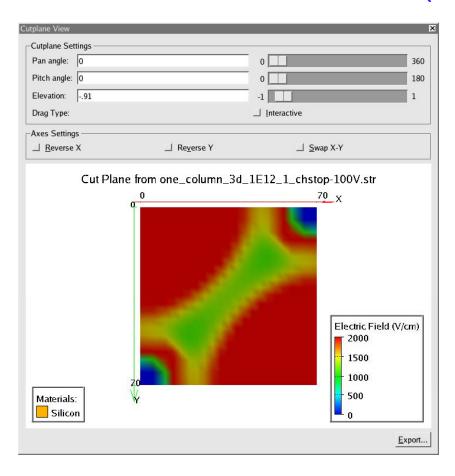


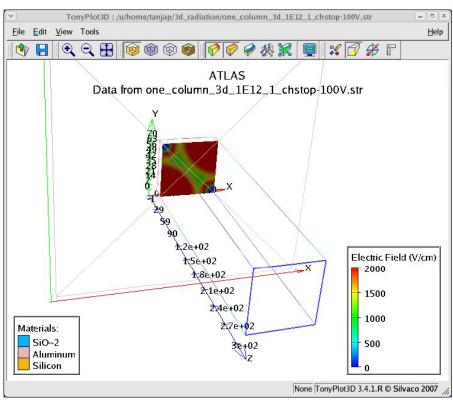


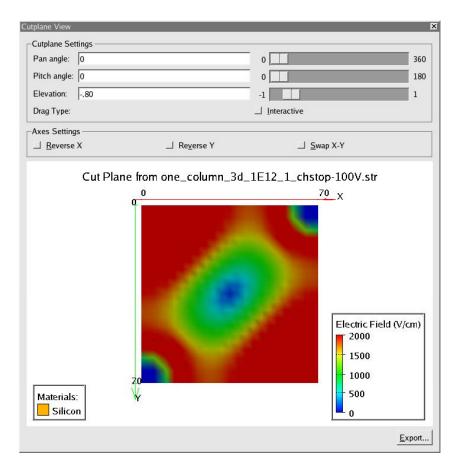


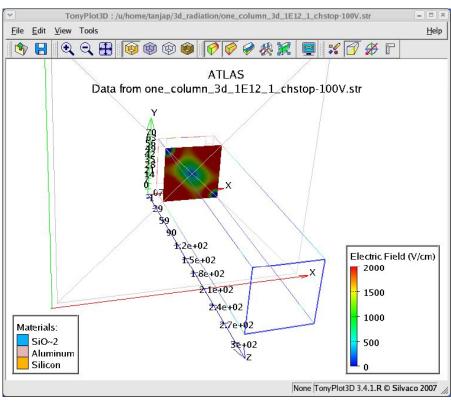


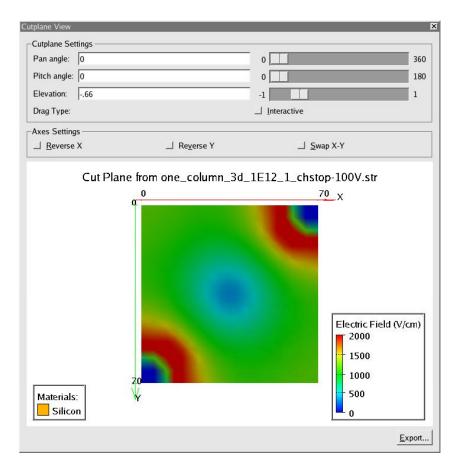


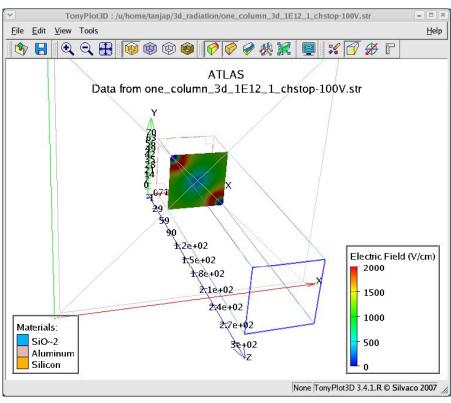


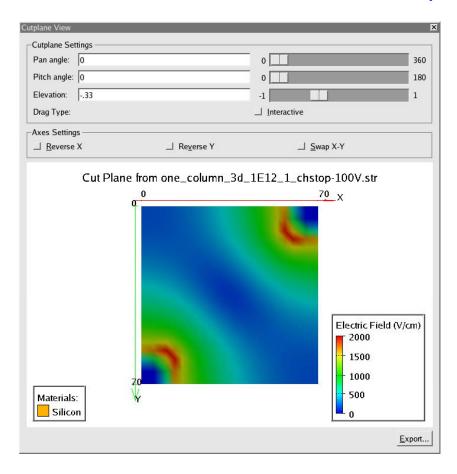


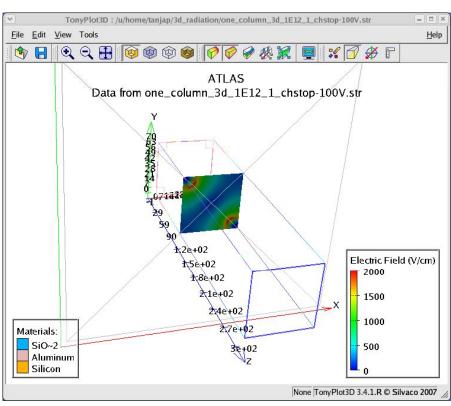


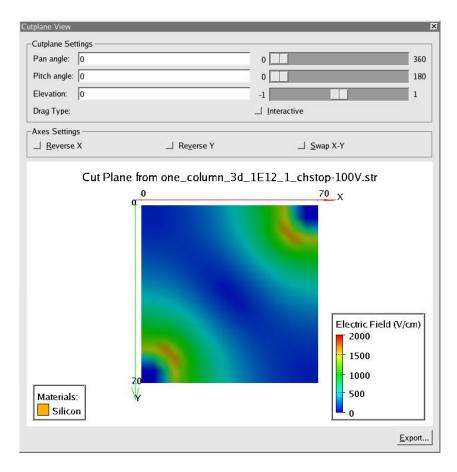


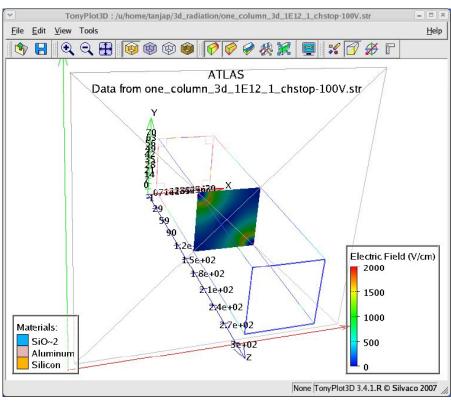


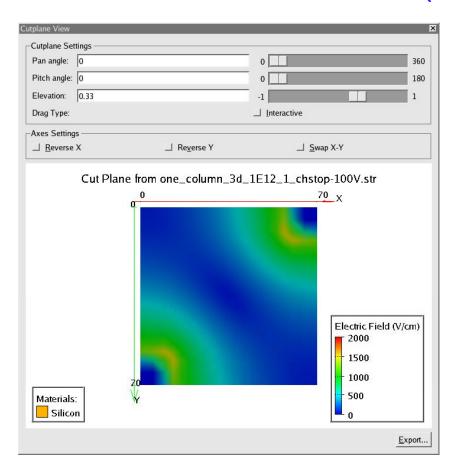


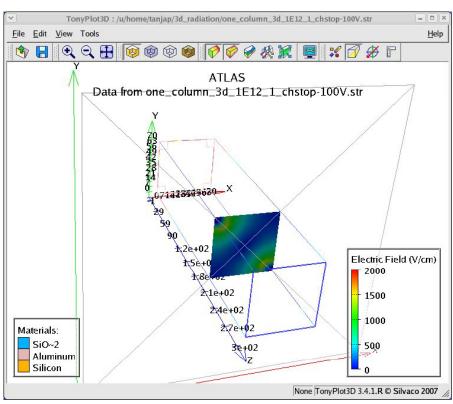


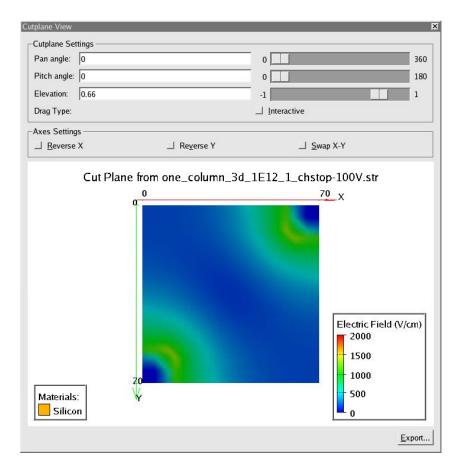


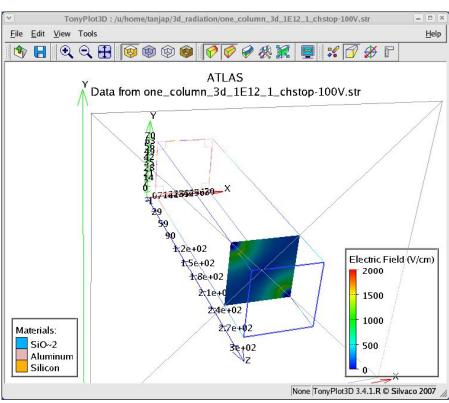


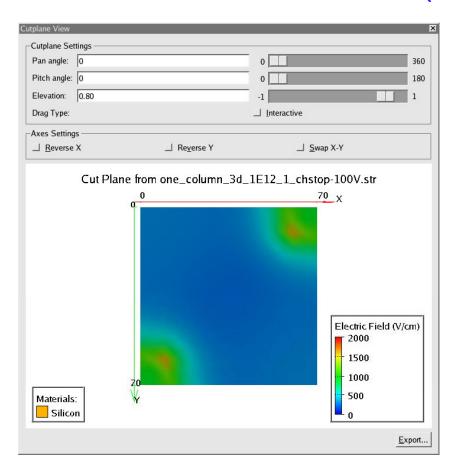


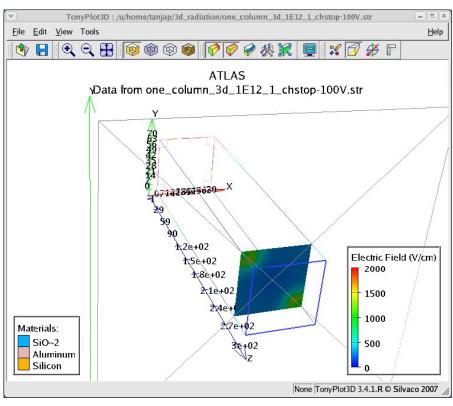


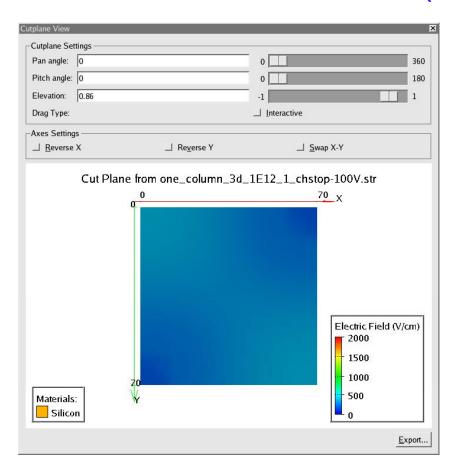


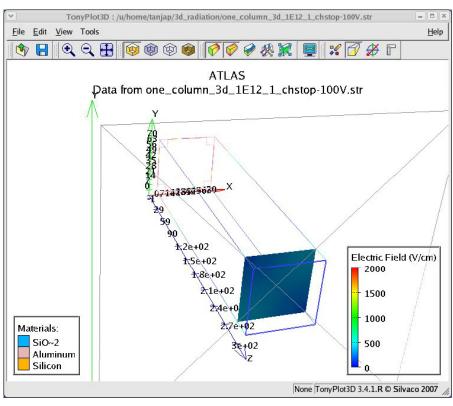


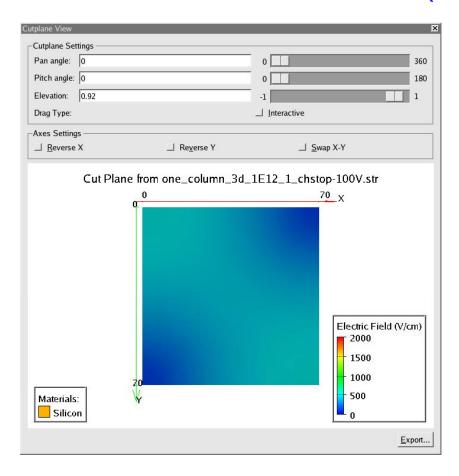


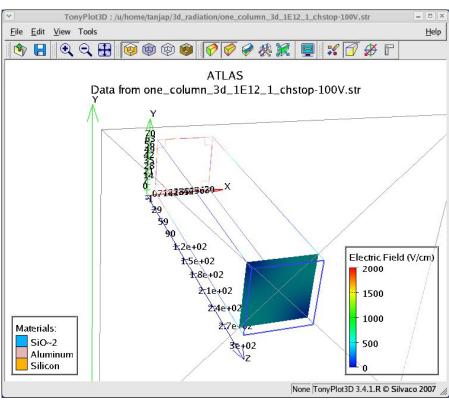


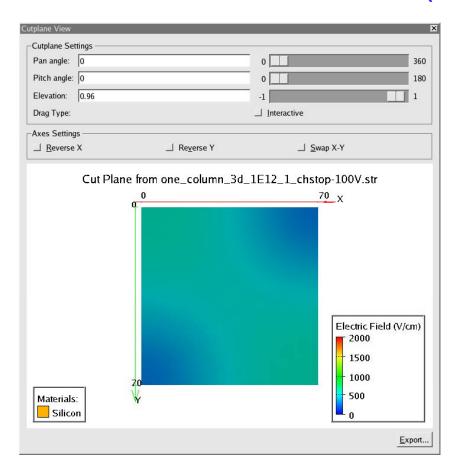


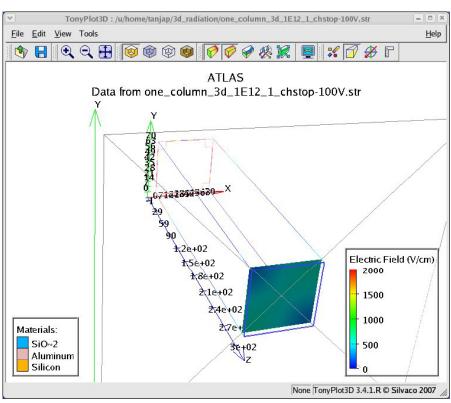


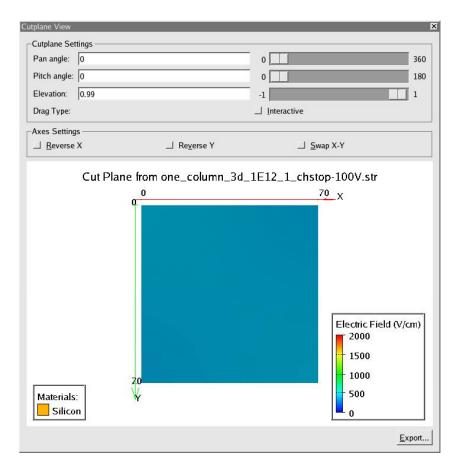


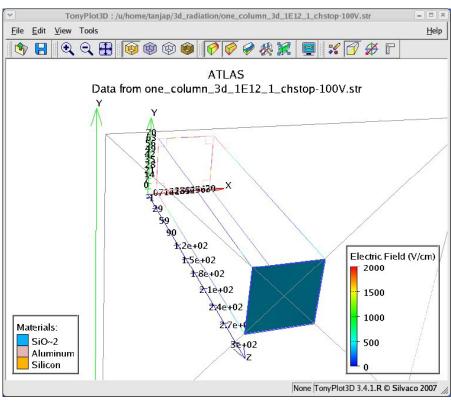


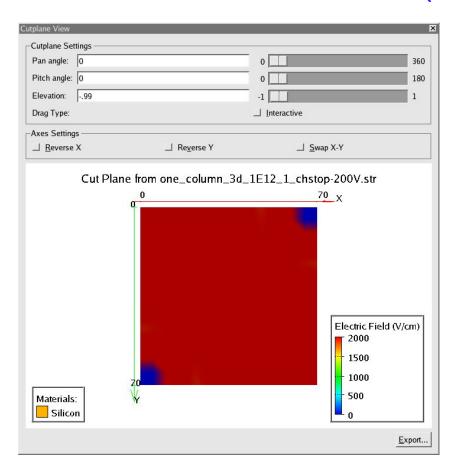


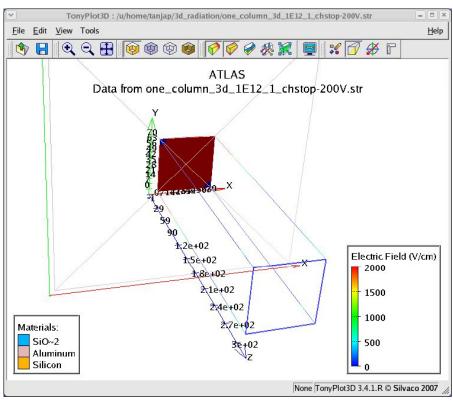


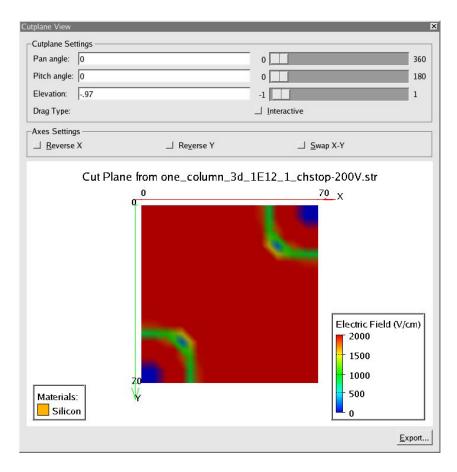


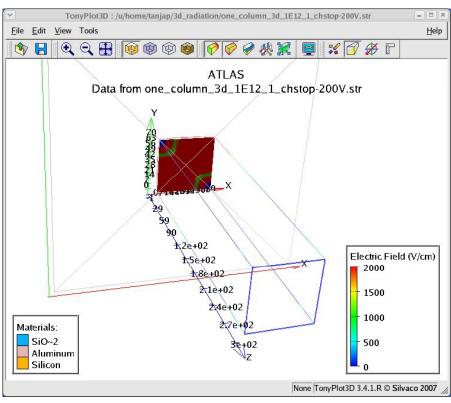


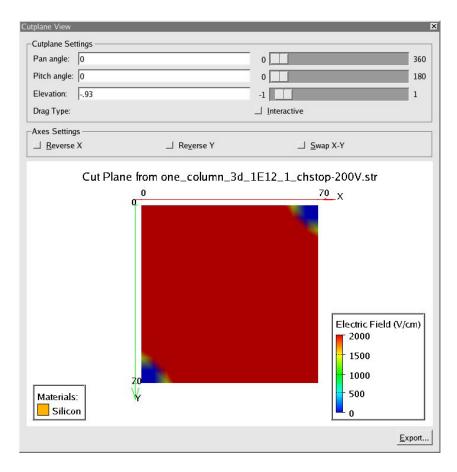


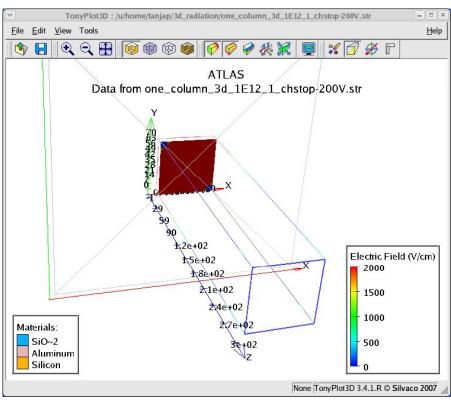


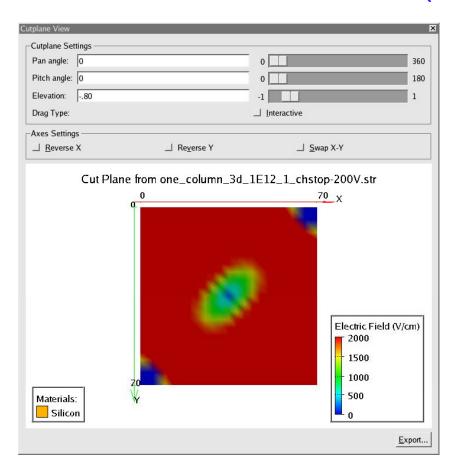


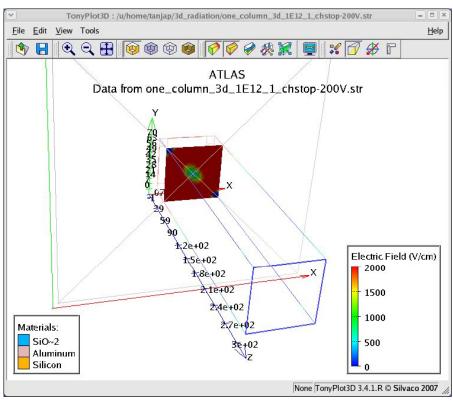


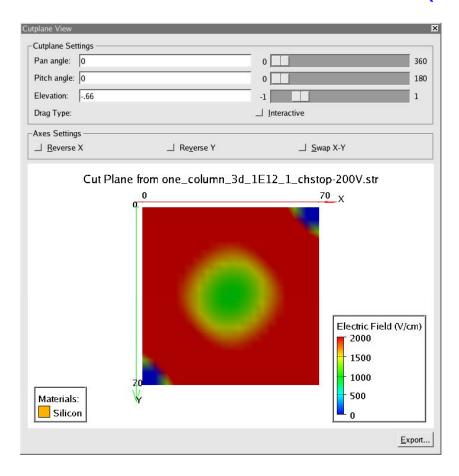


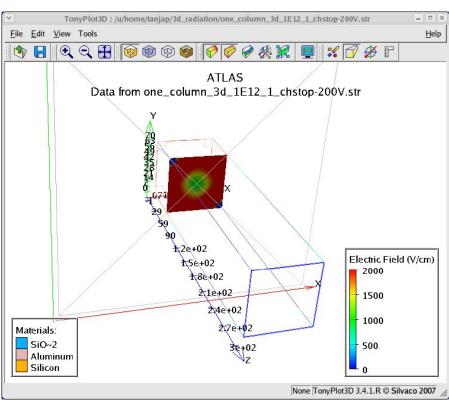


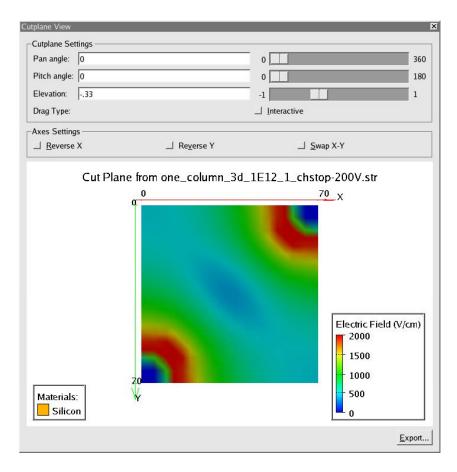


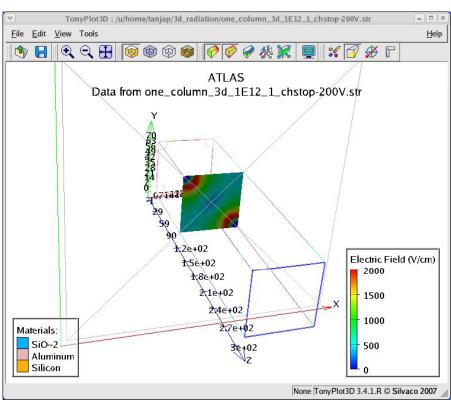


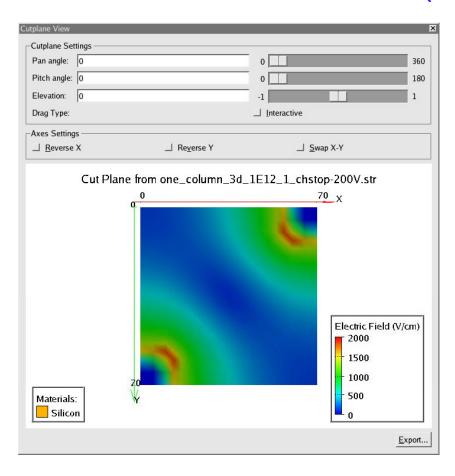


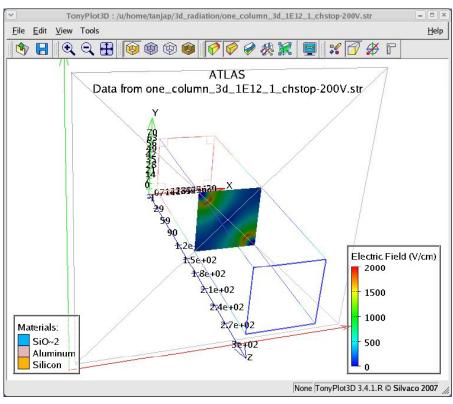


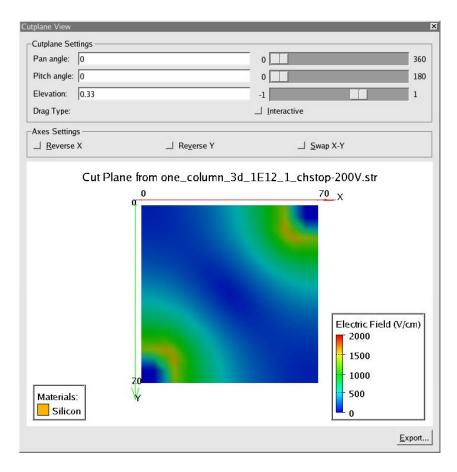


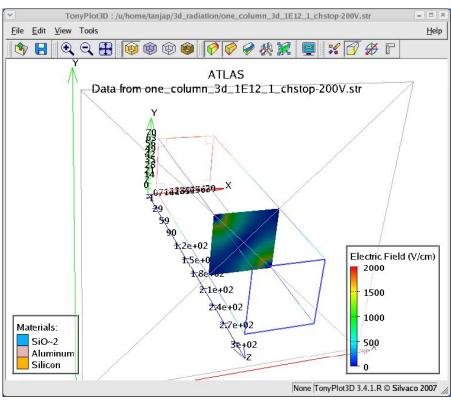


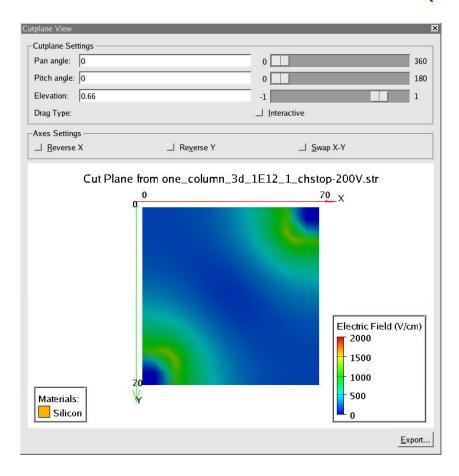


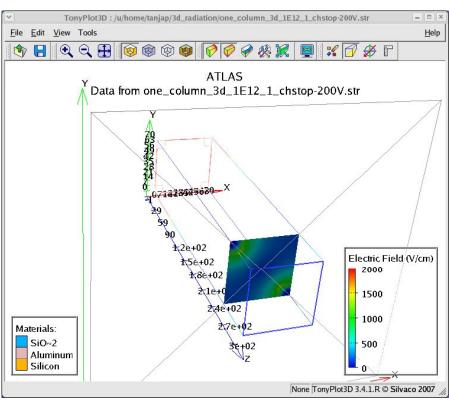


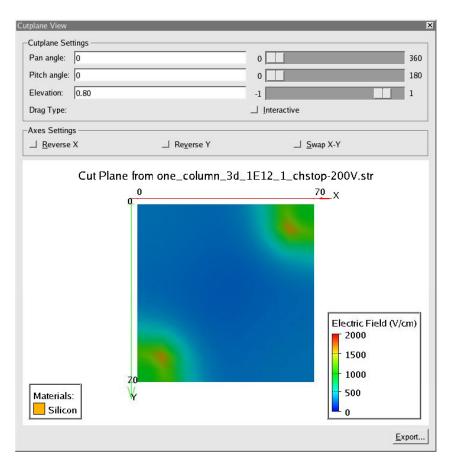


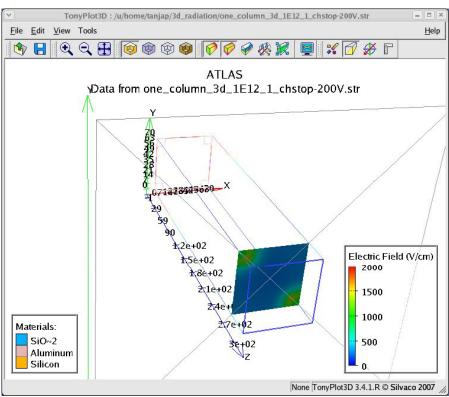


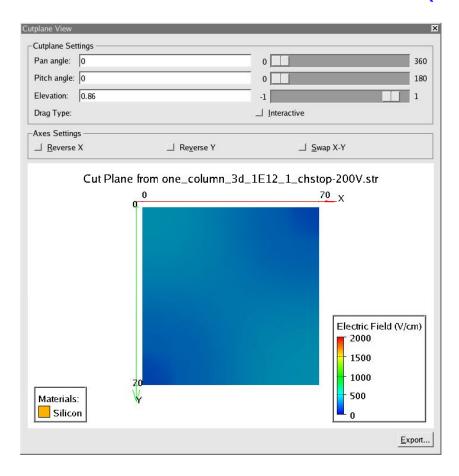


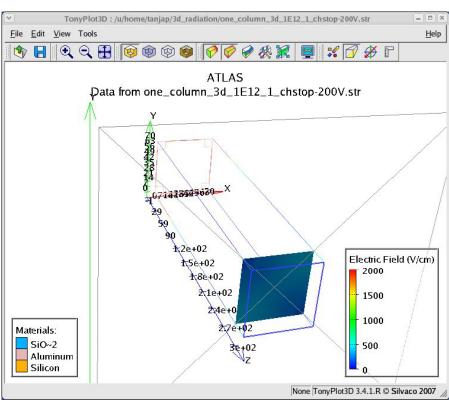


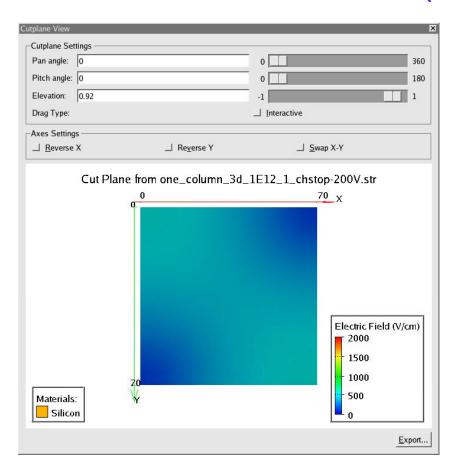


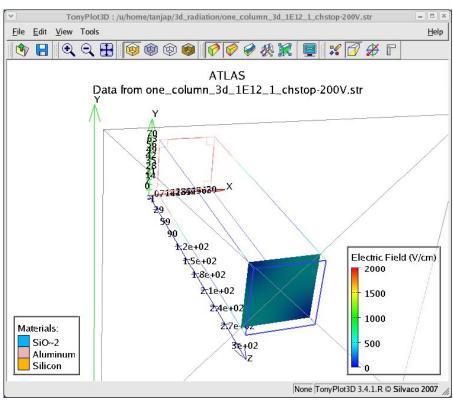


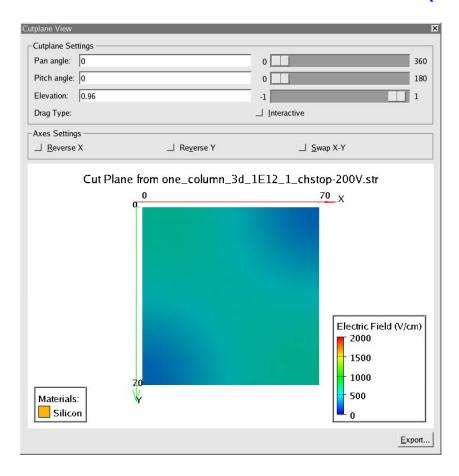


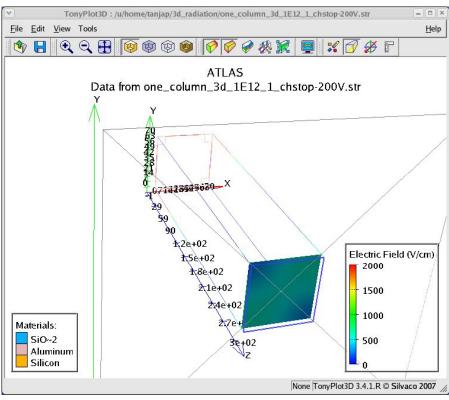


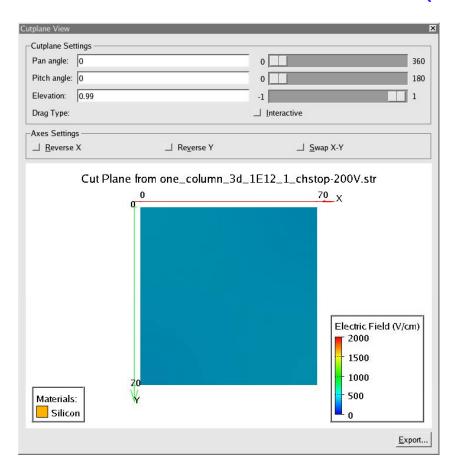


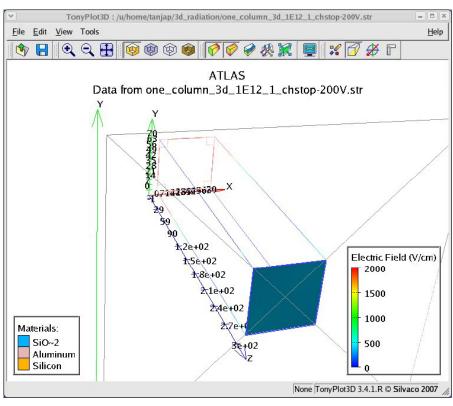






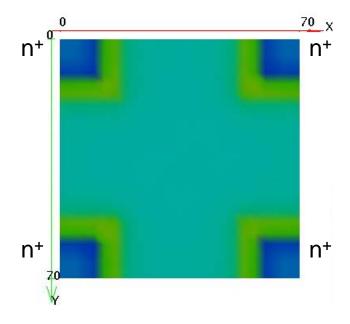


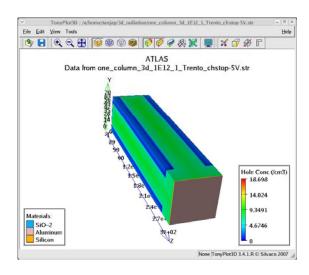




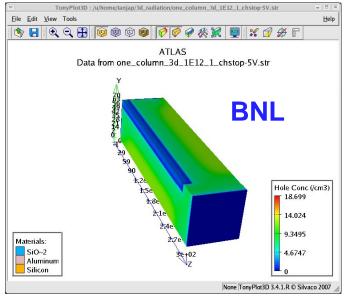
Trento Single column one-sided 3D detector

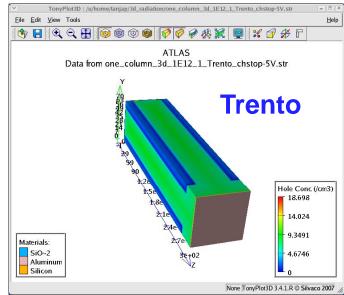
- Trento
- N-type columns penetrate to the p-type bulk from the top surface
- N-columns are surrounded by p-stops

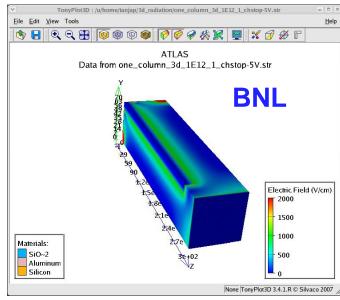




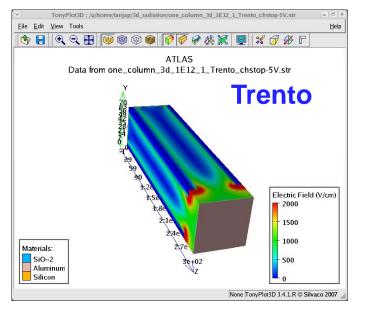
Hole concentration



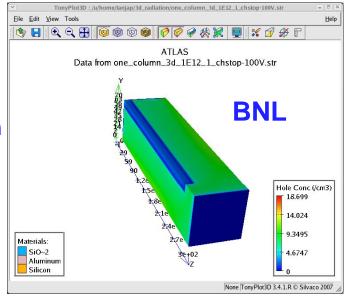


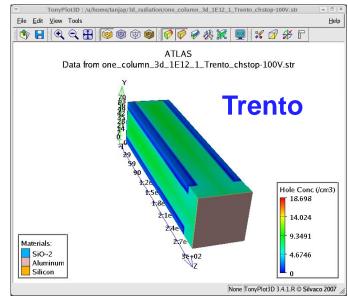


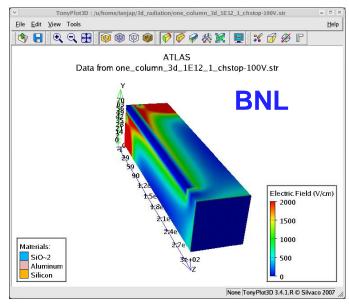


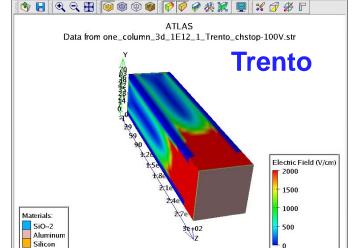


Hole concentration







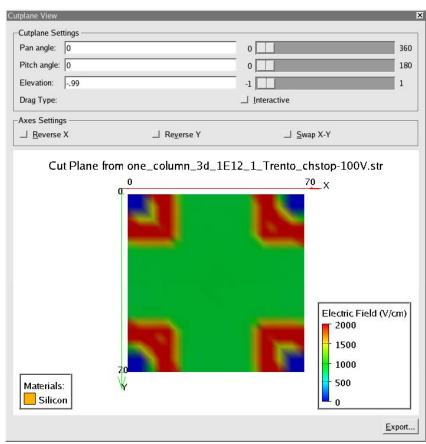


None TonyPlot3D 3.4.1.R © Silvaco 2007

TonyPlot3D: /u/home/tanjap/3d_radiation/one_column_3d_1E12_1_Trento_chstop-100V.str

BNL -Cutplane Settings Pan angle: 0 Pitch angle: 0 Elevation: -.99 __ Interactive Drag Type: -Axes Settings ☐ Reverse Y Cut Plane from one_column_3d_1E12_1_chstop-100V.str 70 X Electric Field (V/cm) 2000 1500 1000 - 500 Materials: Silicon

Trento



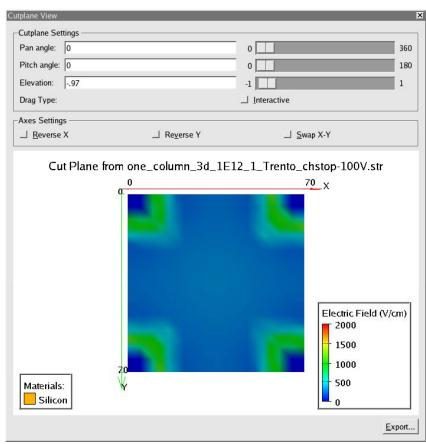
1 µm from the front surface

Export...

Insert microns to explain where the cut is taken tanjap, 4/13/2007

BNL -Cutplane Settings Pan angle: 0 Pitch angle: 0 Elevation: -.97 Drag Type: __ Interactive -Axes Settings ☐ Reverse Y Cut Plane from one_column_3d_1E12_1_chstop-100V.str Electric Field (V/cm) 2000 1500 1000 500 Materials: Silicon Export...

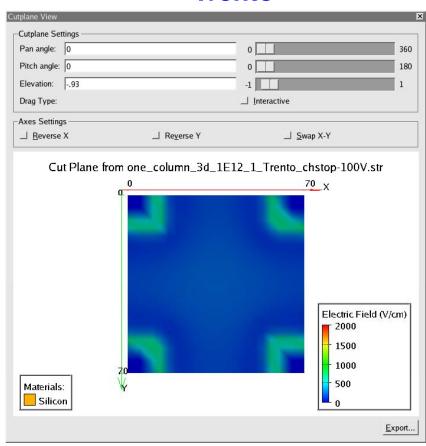
Trento



5 µm from the front surface

BNL -Cutplane Settings Pan angle: 0 Pitch angle: 0 Elevation: -.93 Drag Type: __ Interactive -Axes Settings ☐ Reverse Y Cut Plane from one_column_3d_1E12_1_chstop-100V.str 70 X Electric Field (V/cm) 2000 1500 1000 - 500 Materials: Silicon Export...

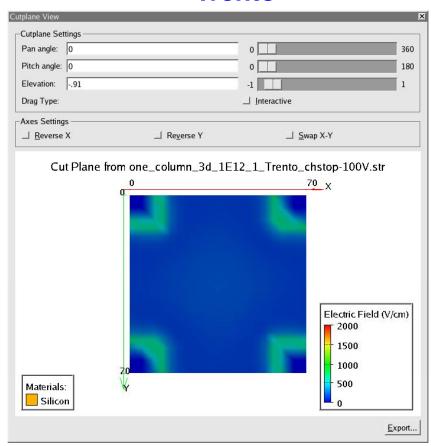
Trento



10 µm from the front surface

BNL -Cutplane Settings Pan angle: 0 360 Pitch angle: 0 180 Elevation: -.91 Drag Type: __ Interactive -Axes Settings ☐ Reverse Y Cut Plane from one_column_3d_1E12_1_chstop-100V.str 70 X Electric Field (V/cm) 2000 1500 1000 500 Materials: Silicon Export...

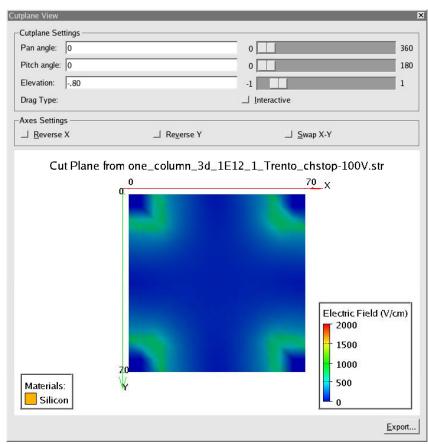
Trento



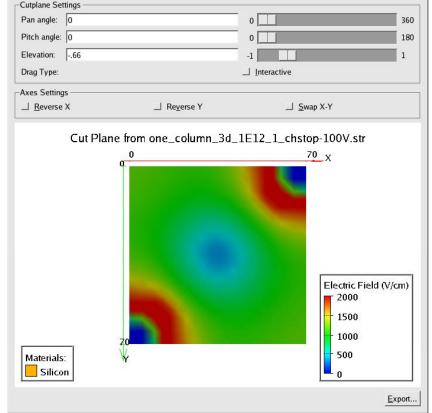
15 µm from the front surface

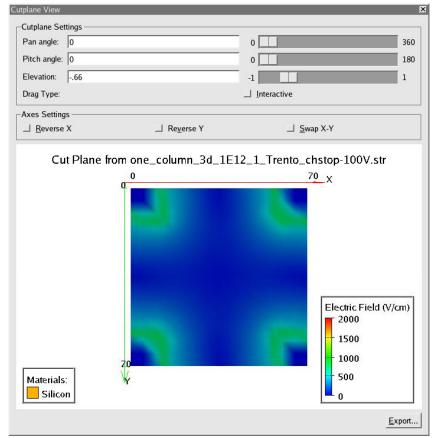
BNL -Cutplane Settings Pan angle: 0 Pitch angle: 0 Elevation: -.80 Drag Type: __ Interactive -Axes Settings ☐ Reverse Y Cut Plane from one_column_3d_1E12_1_chstop-100V.str 70 X Electric Field (V/cm) 2000 1500 1000 - 500 Materials: Silicon Export...

Trento

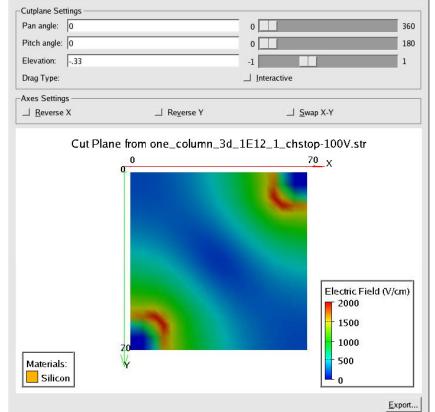


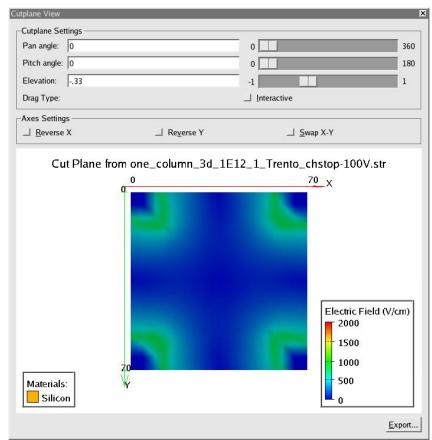
30 µm from the front surface





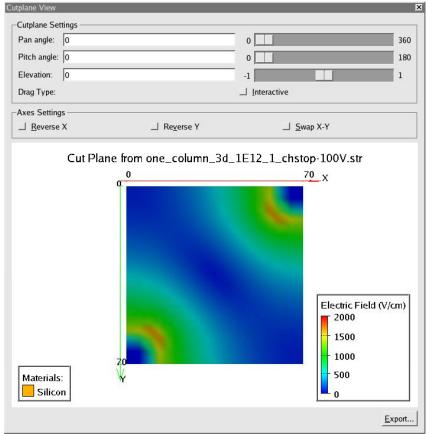
50 µm from the front surface

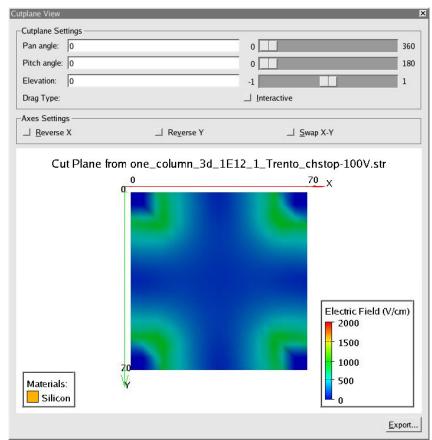




100 µm from the front surface

BNL Trento



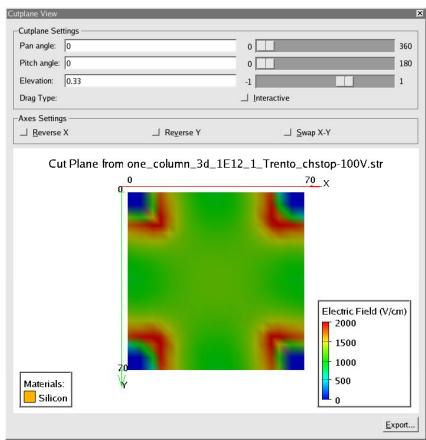


150 µm from the front surface

BNL -Cutplane Settings Pan angle: 0 Pitch angle: 0 Elevation: 0.33 __ Interactive Drag Type: -Axes Settings ☐ Reverse Y Cut Plane from one_column_3d_1E12_1_chstop-100V.str 70 X Electric Field (V/cm) 2000 1500 1000 - 500 Materials:

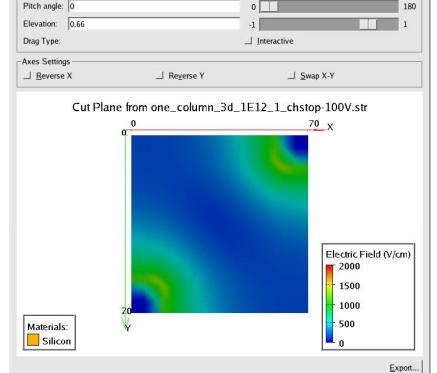
Silicon

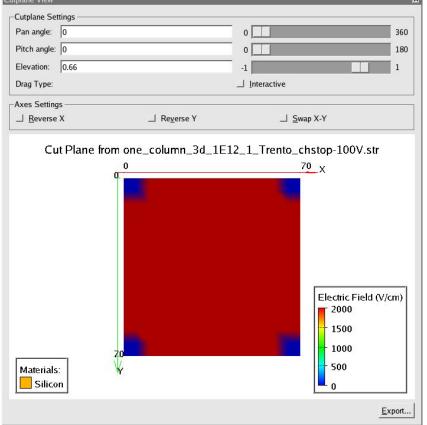
Trento



200 µm from the front surface

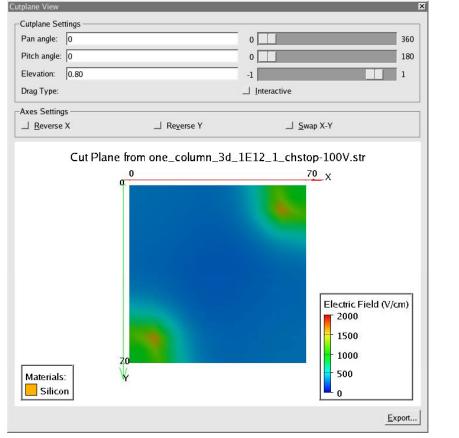
Export...

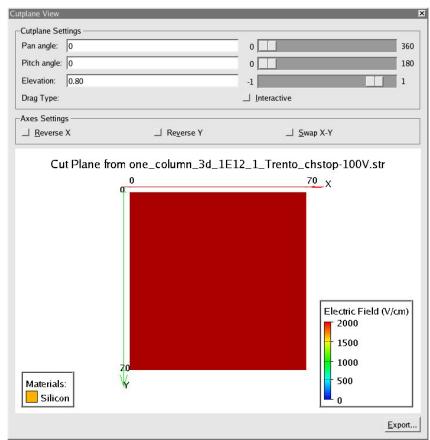




250 µm from the front surface

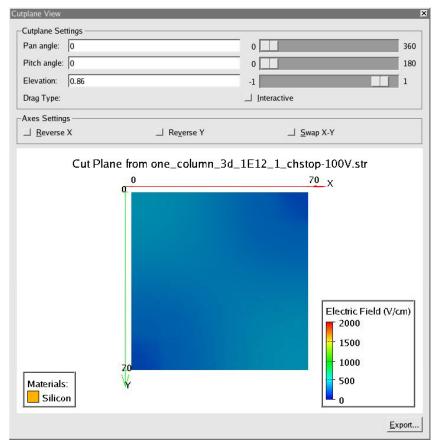
BNL Trento

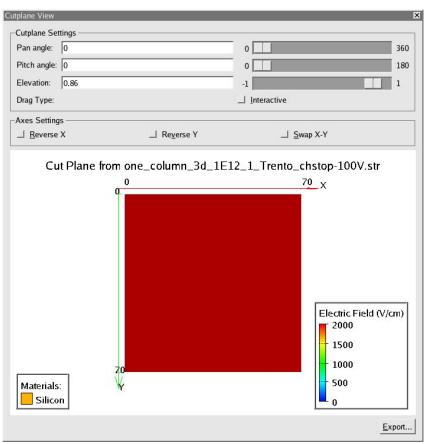




270 µm from the front surface

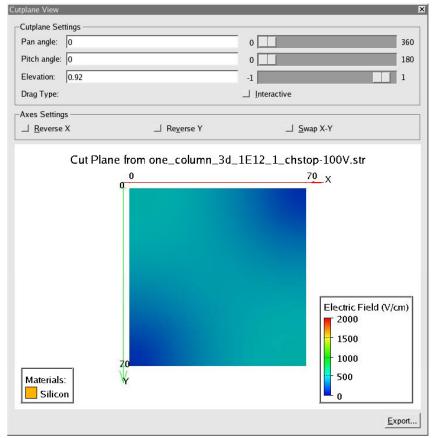
BNL Trento

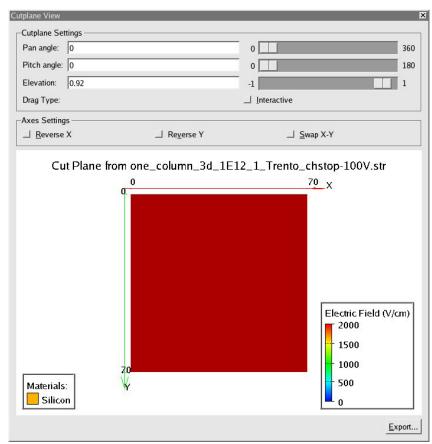




280 µm from the front surface

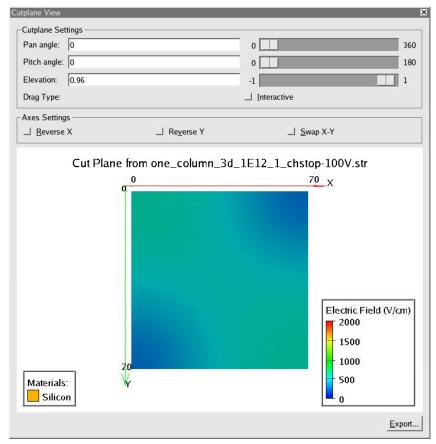
BNL Trento

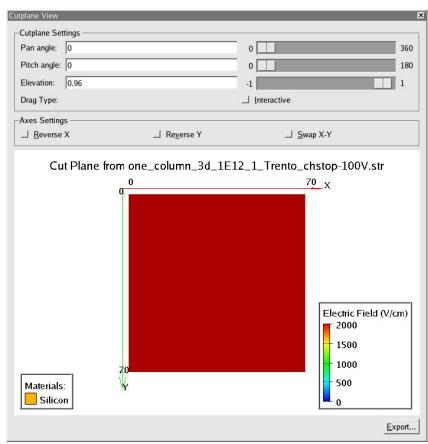




290 µm from the front surface

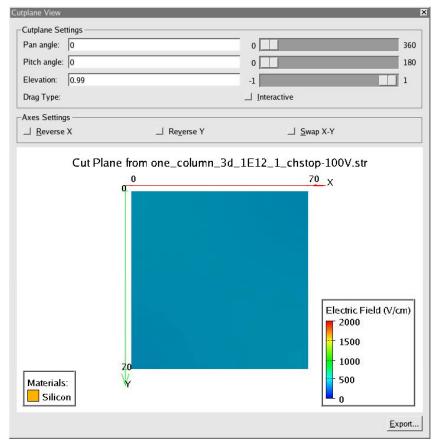
BNL Trento

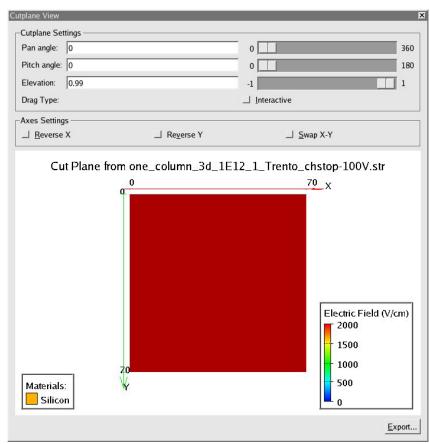




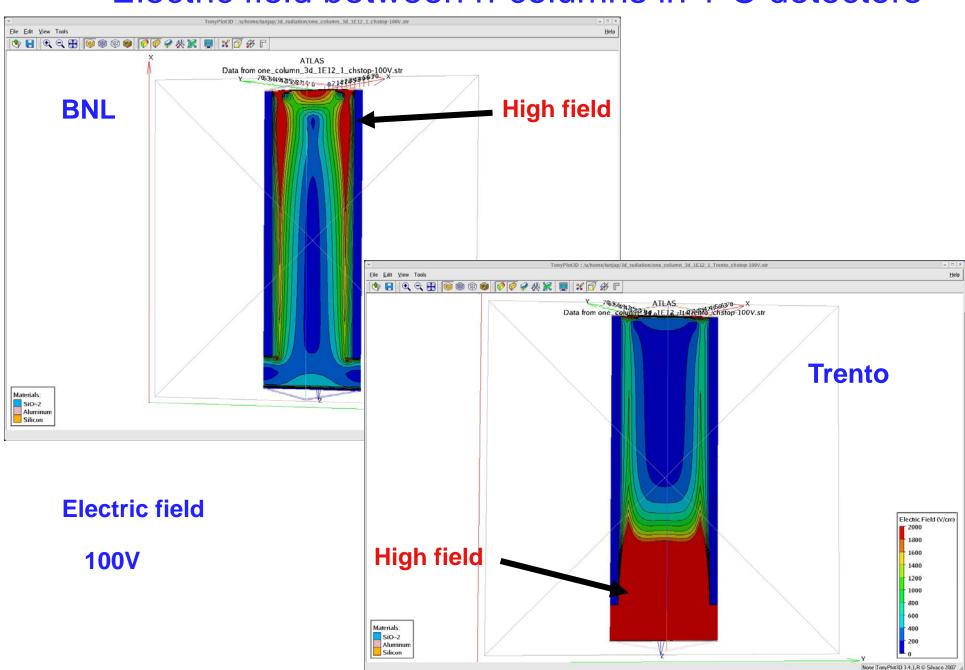
295 µm from the front surface

BNL Trento



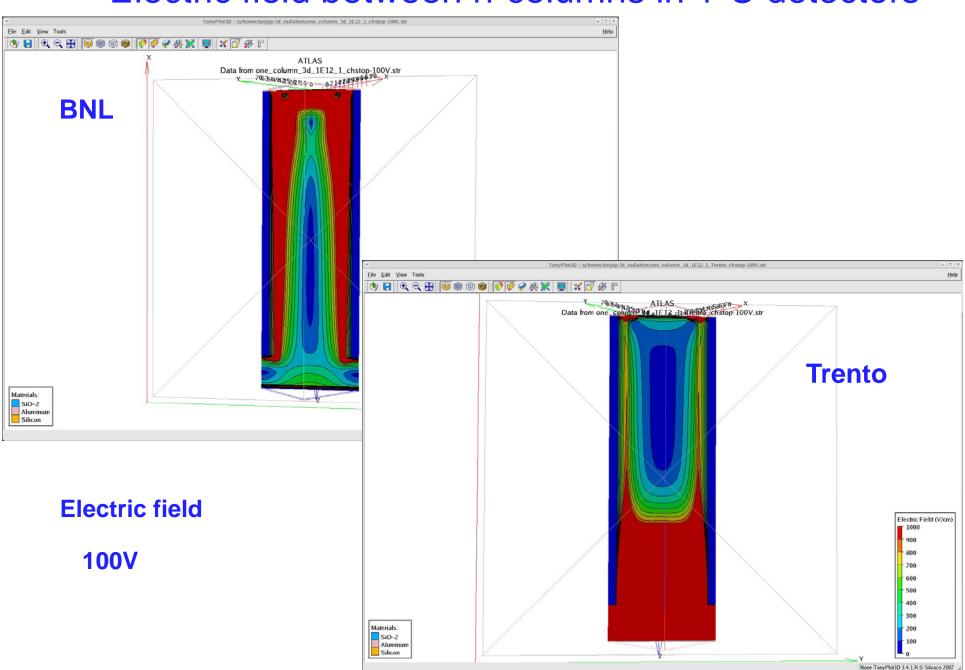


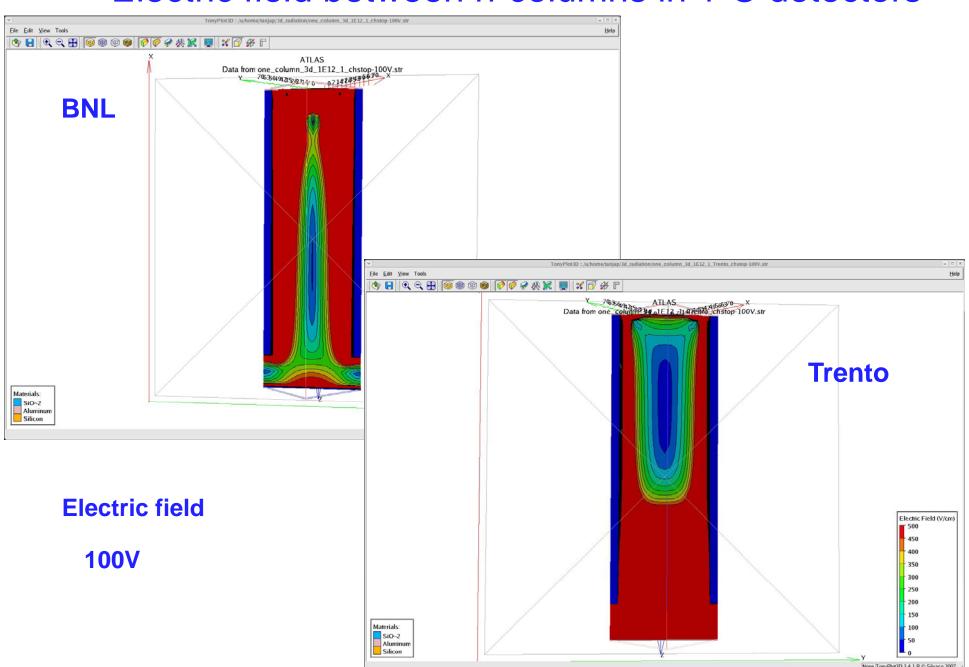
299 µm from the front surface

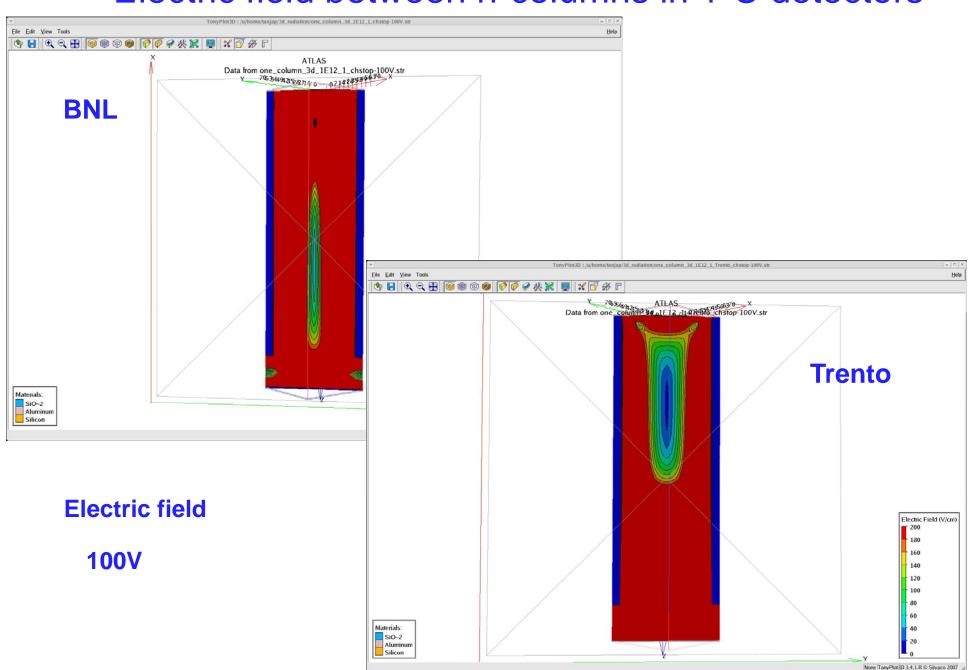


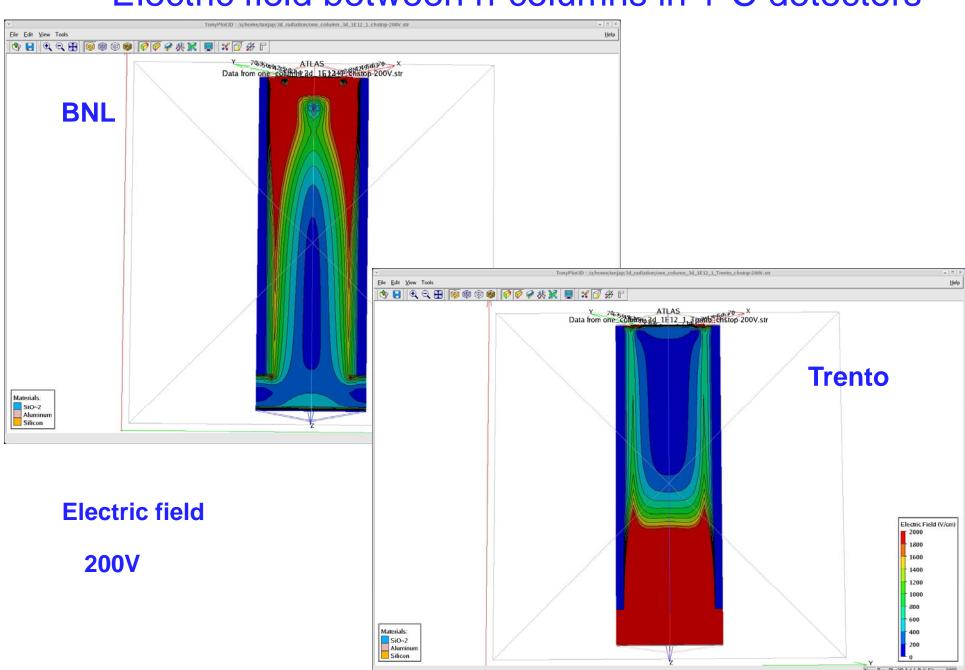
Make an arrow to show where the most of the high field is (fronside-BNL, backside-Trento)

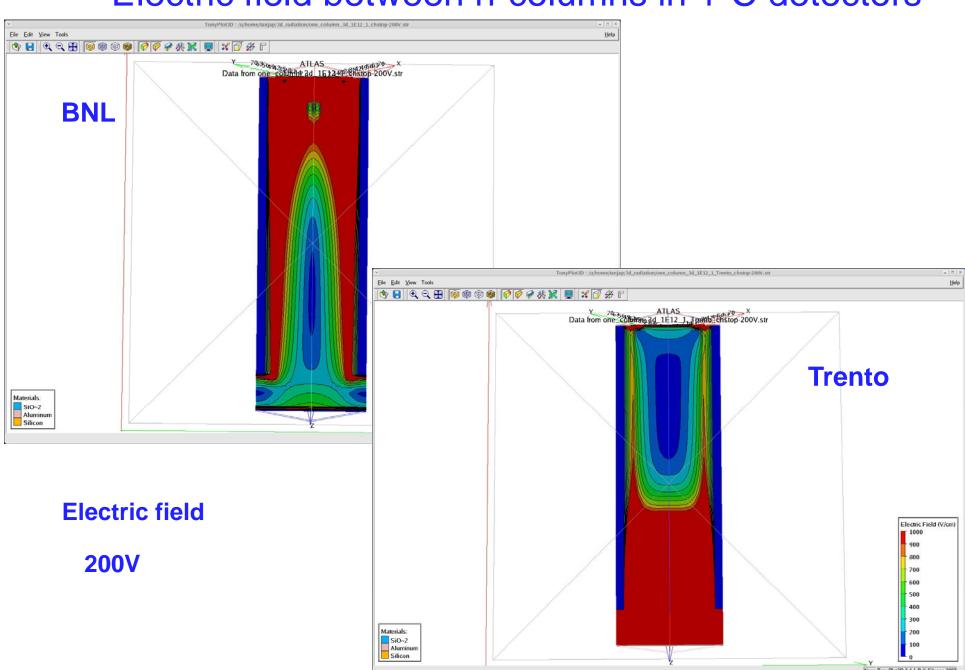
Explain that the cut is same only the scale is changed to see more accurate the field $\frac{1}{3}$

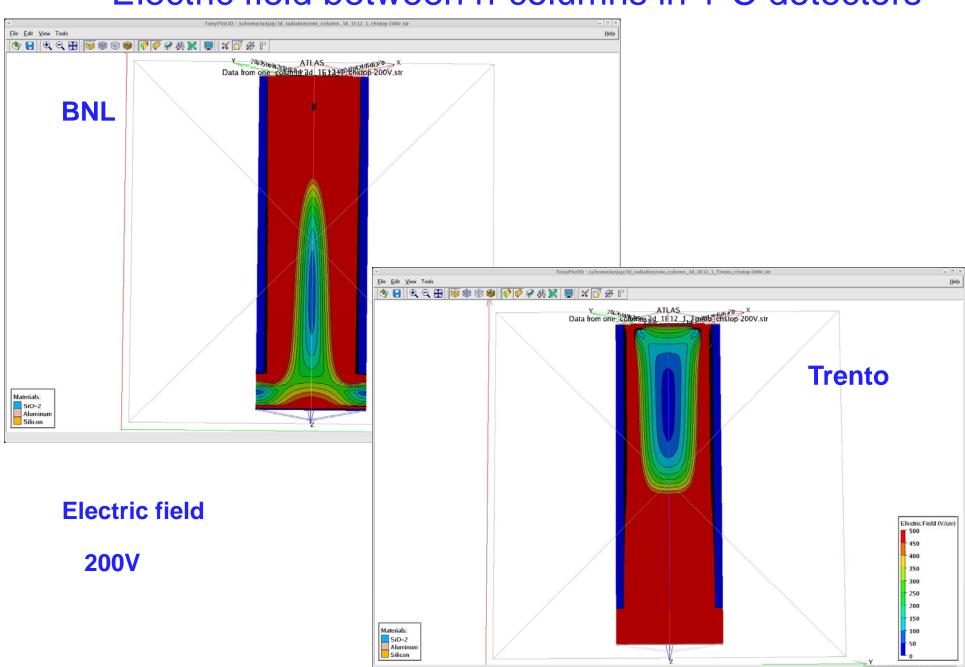


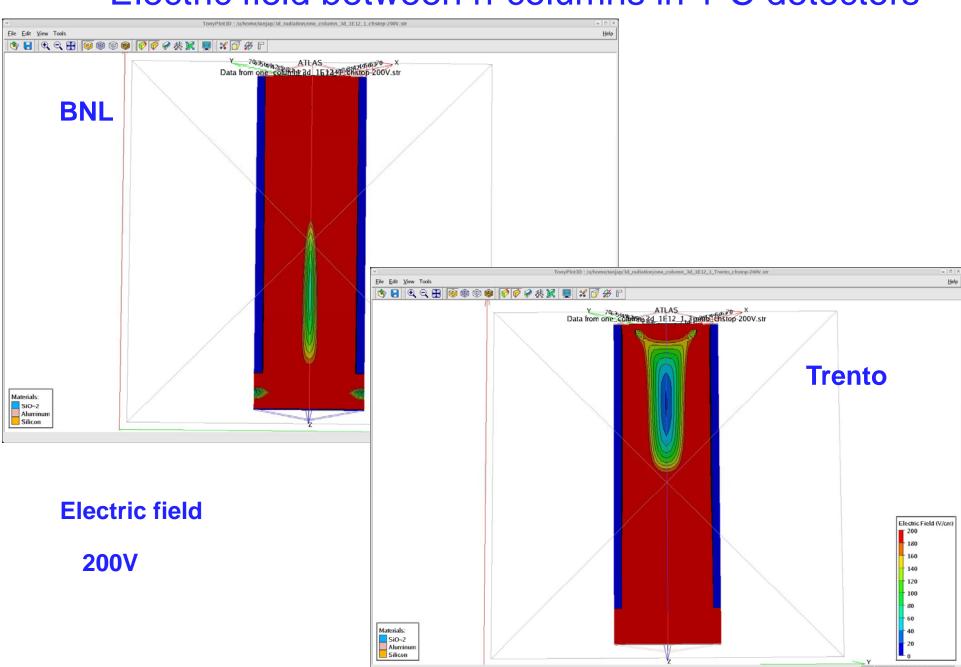






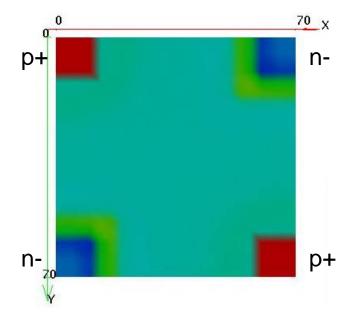


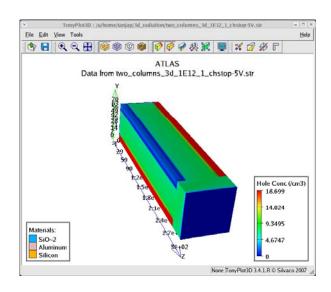




BNL dual column one-sided 3D detector

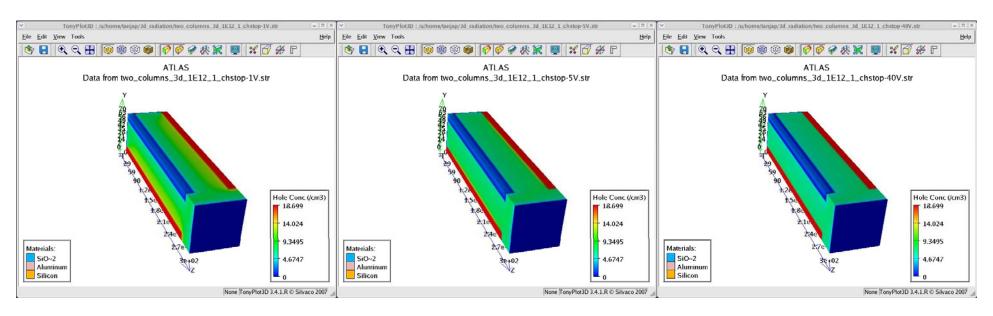
- BNL
- In this structure there are two n-type (blue in the pictures) and two p-type (red in the pictures) doped columns on p-type substrate
- Same type of doped columns are placed to the opposite corners
- N-columns are surrounded by the p-stops
- All columns are 270um long

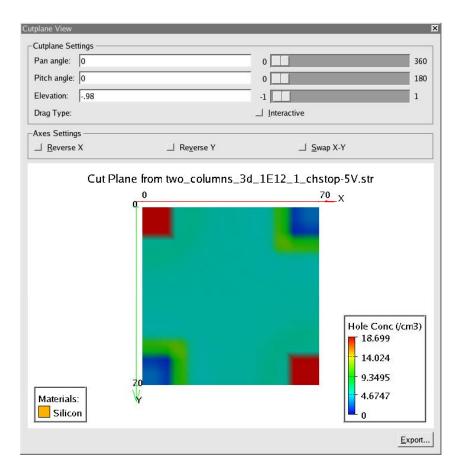


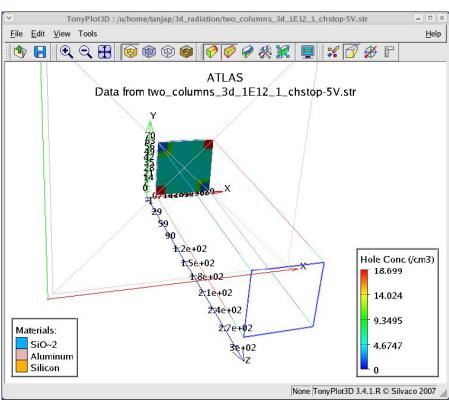


BNL dual column one-sided 3D detector

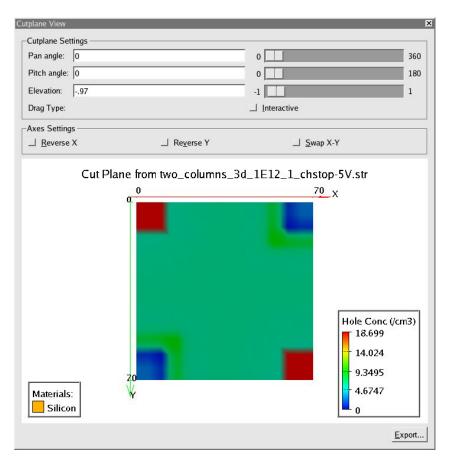


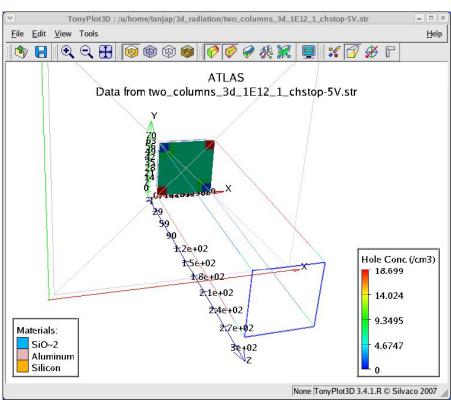


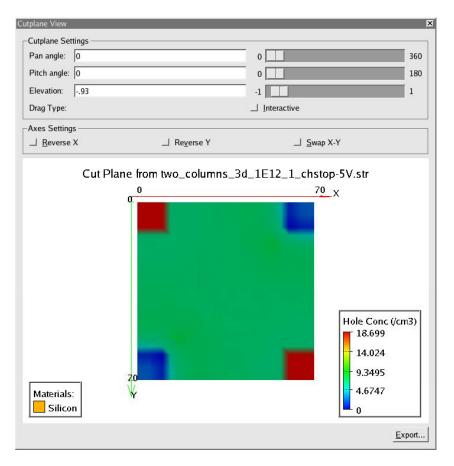


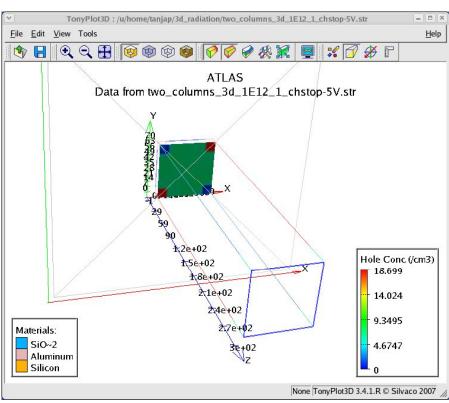


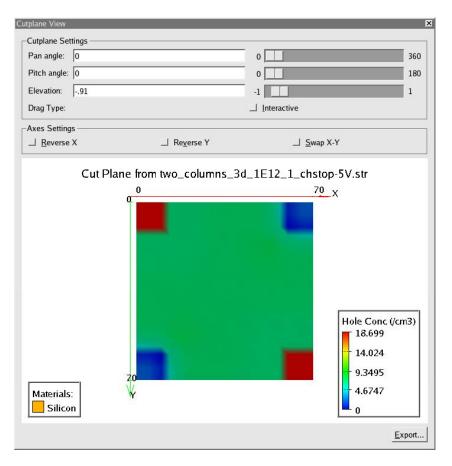
Make a movie tanjap, 4/13/2007

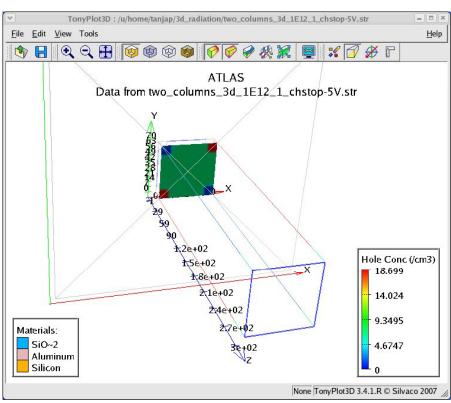


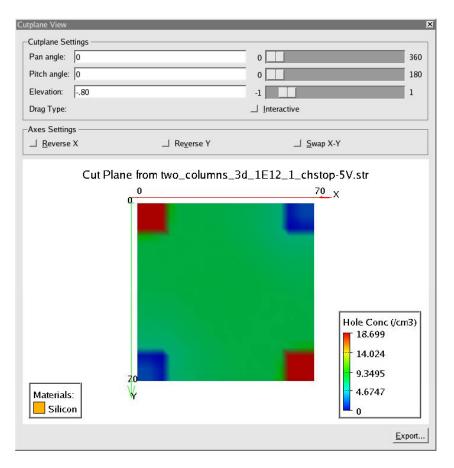


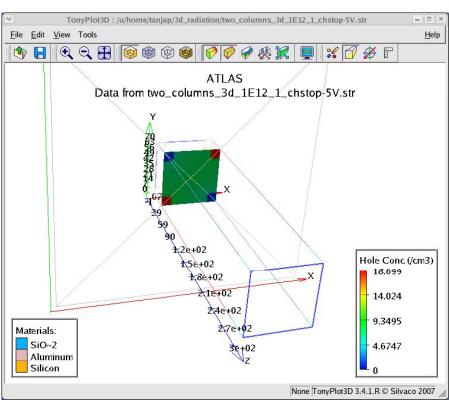


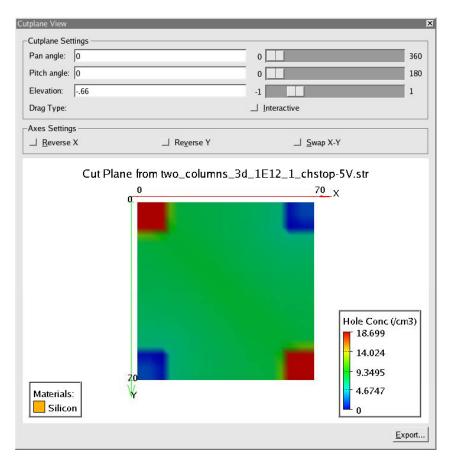


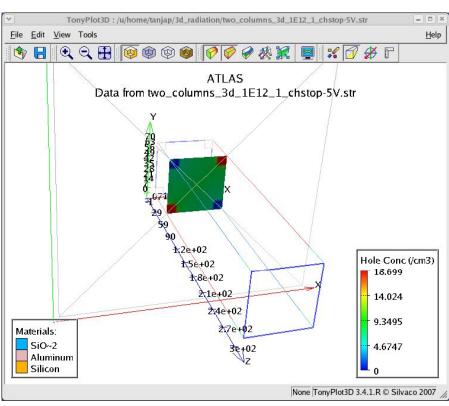


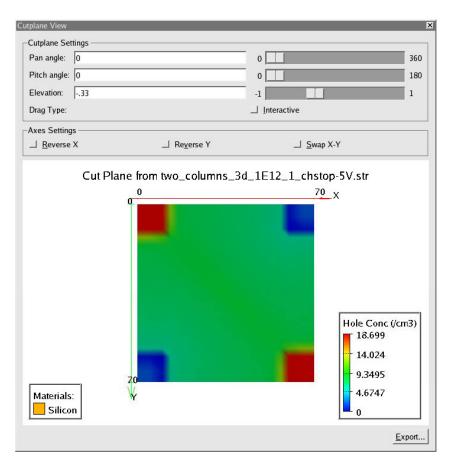


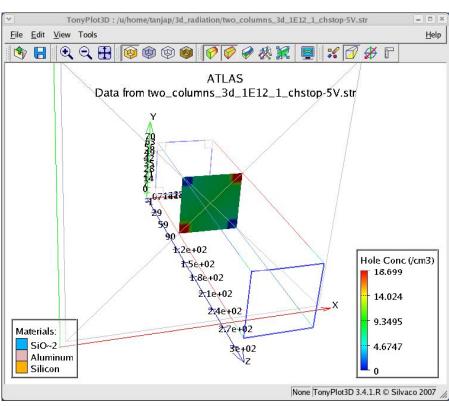


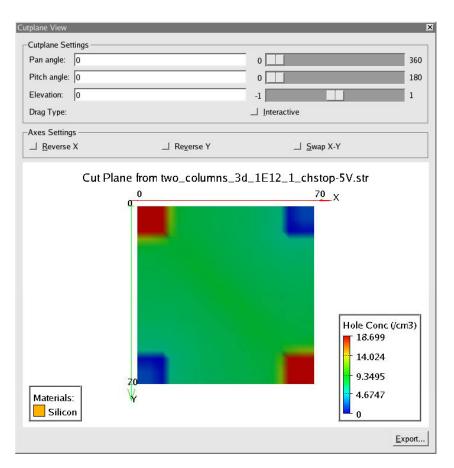


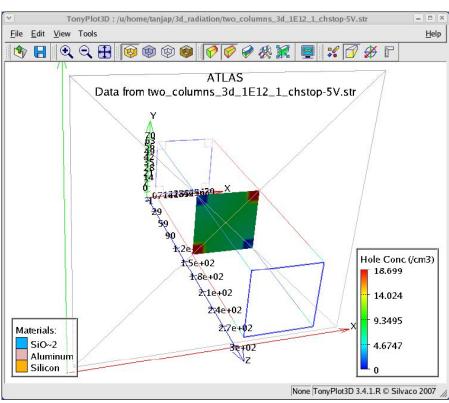


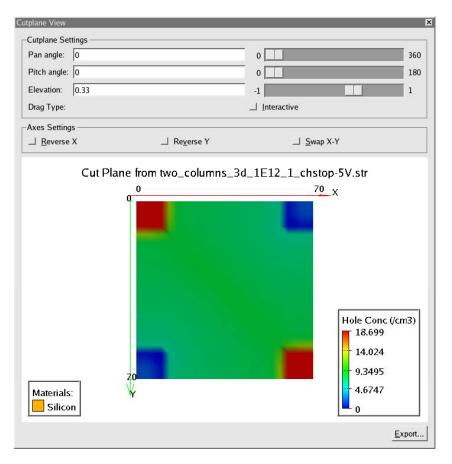


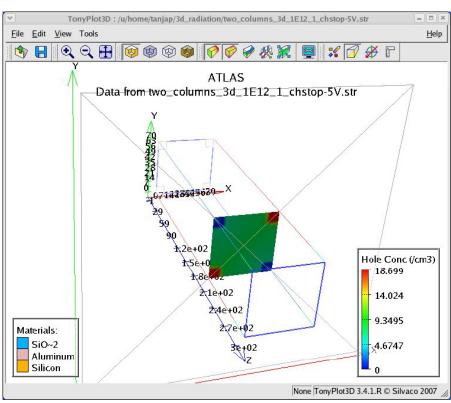


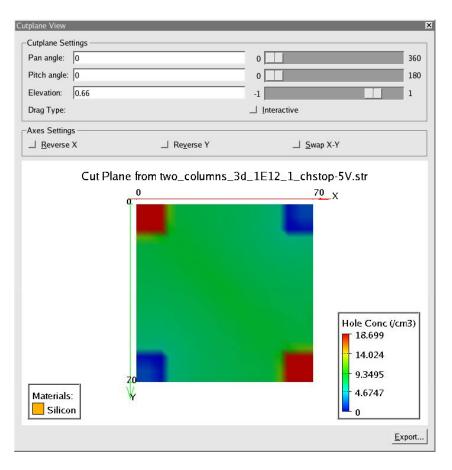


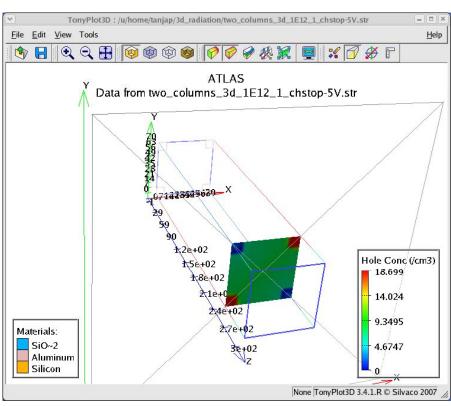


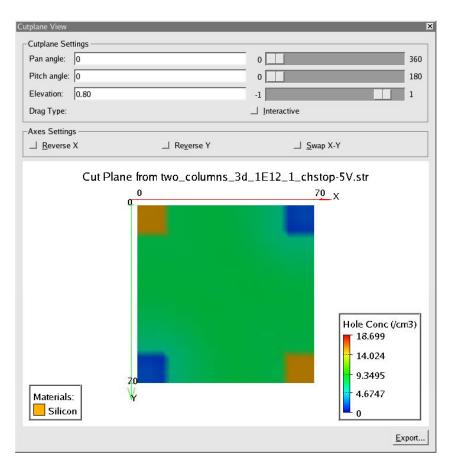


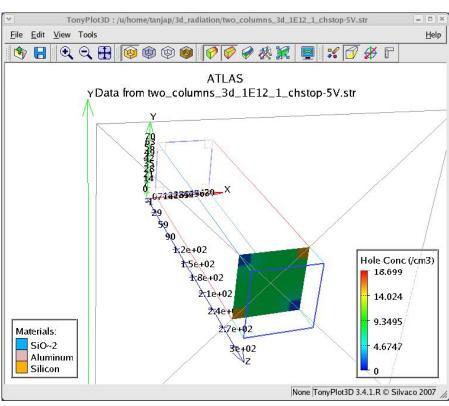


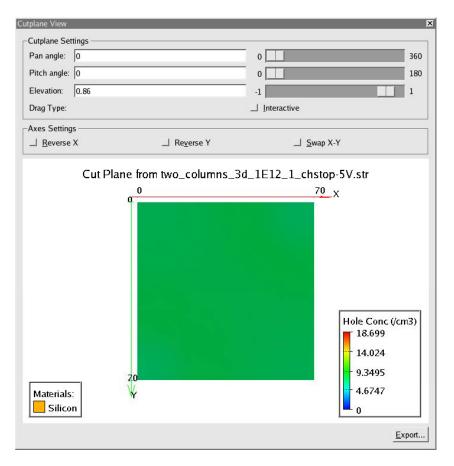


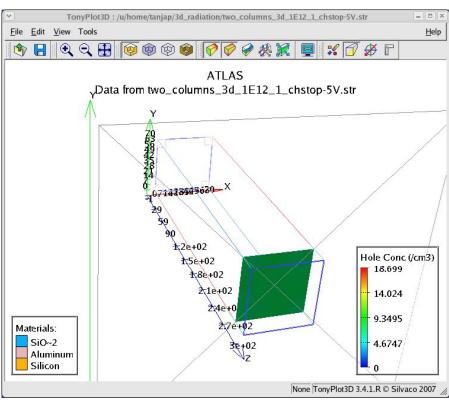


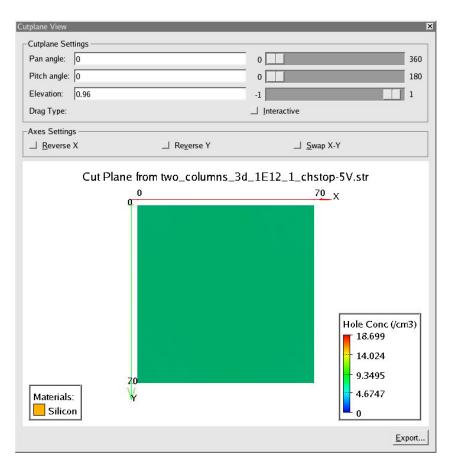


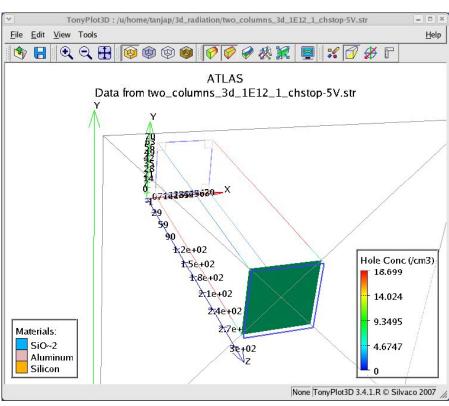




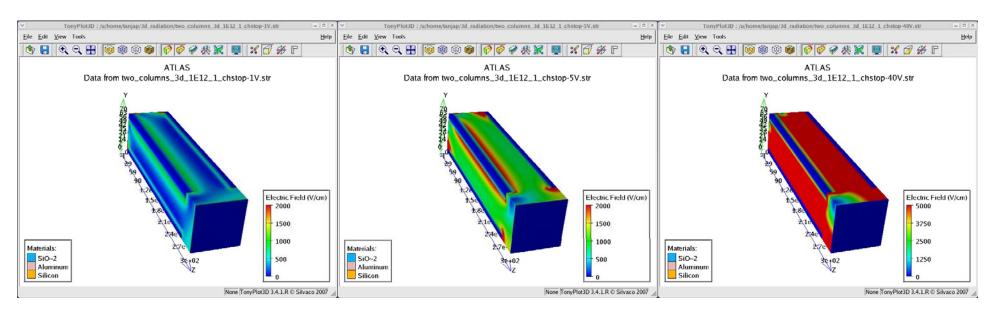


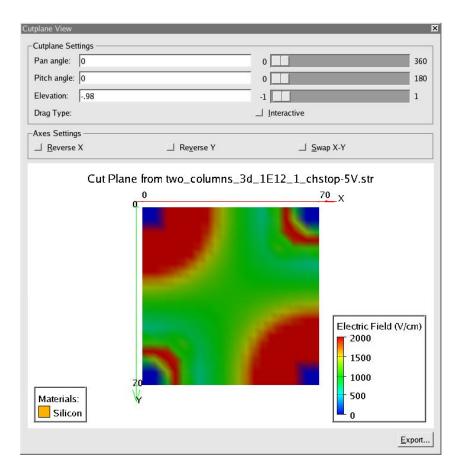


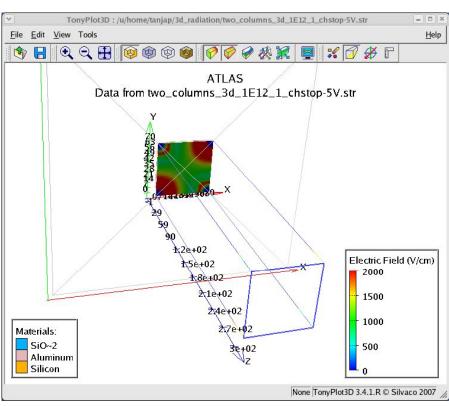


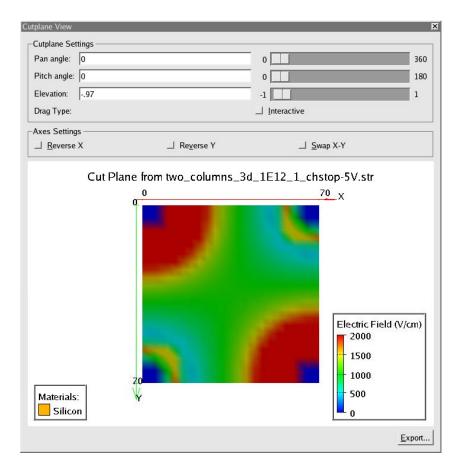


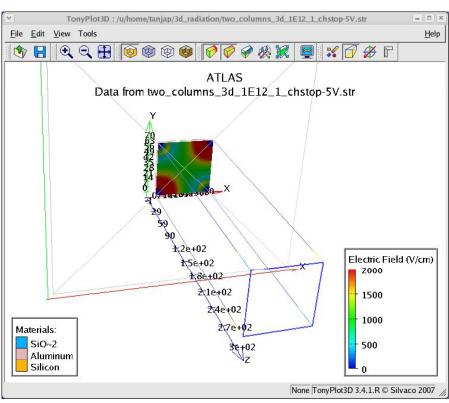
1V 5V 40V

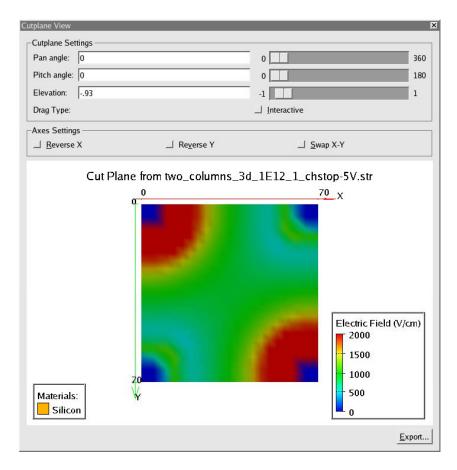


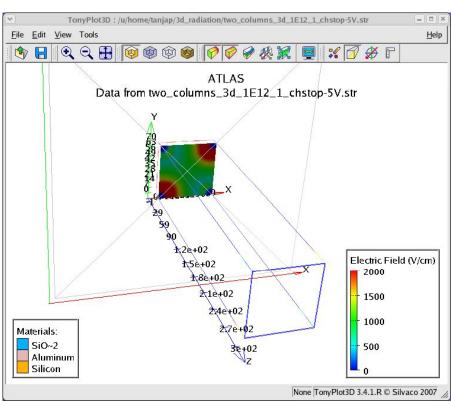


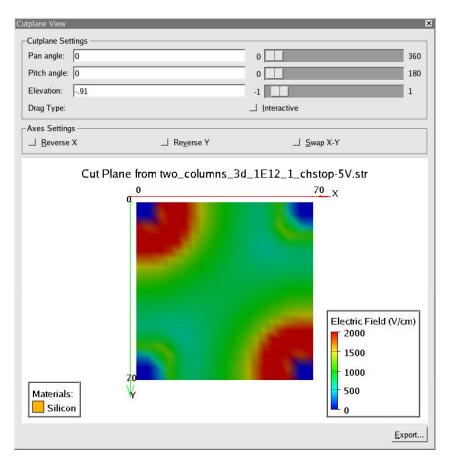


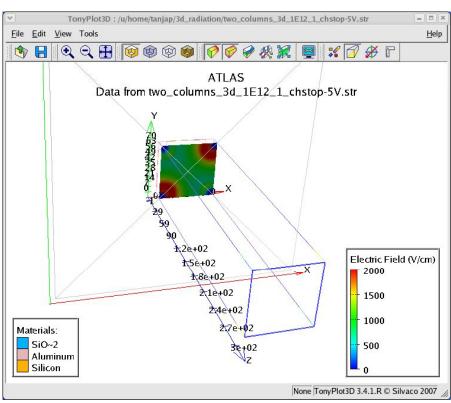


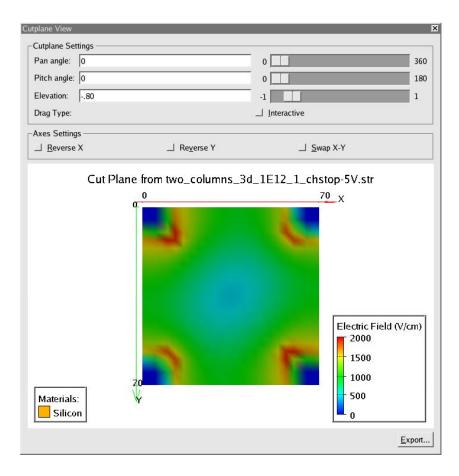


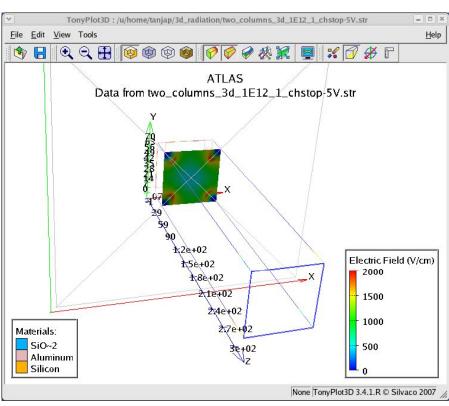


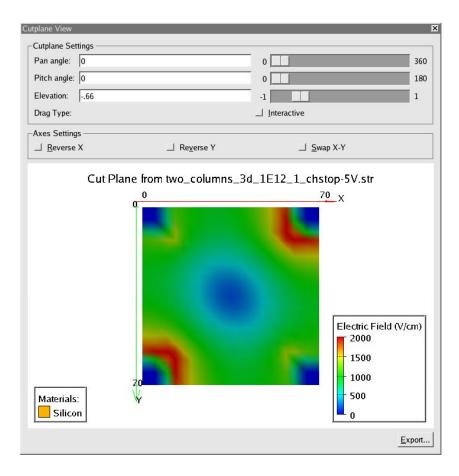


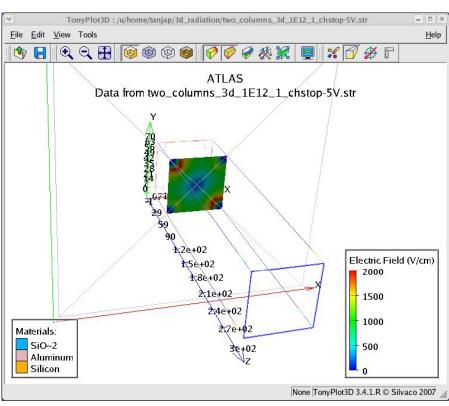


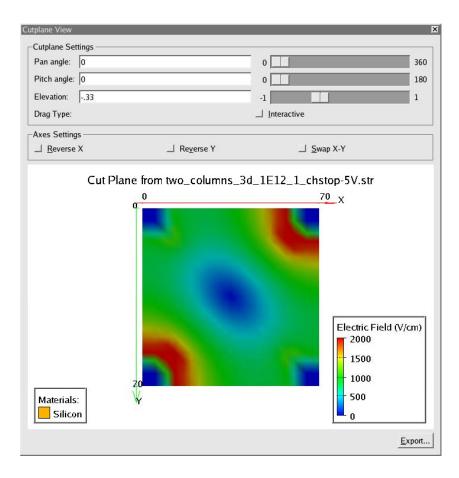


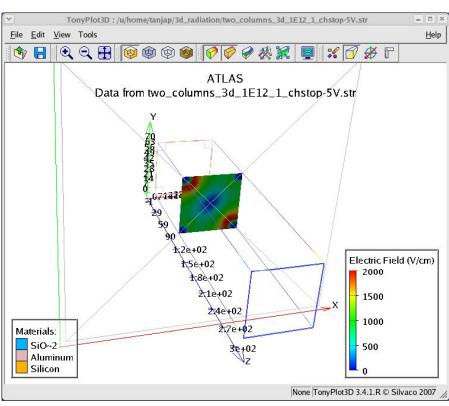


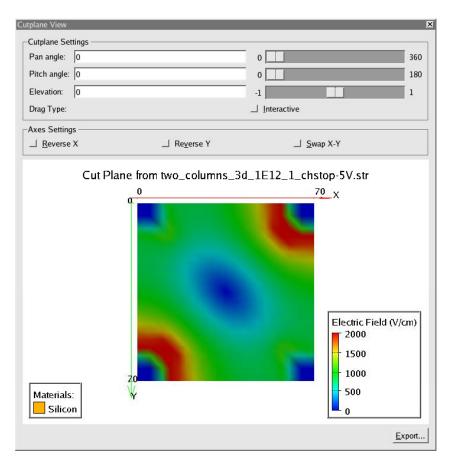


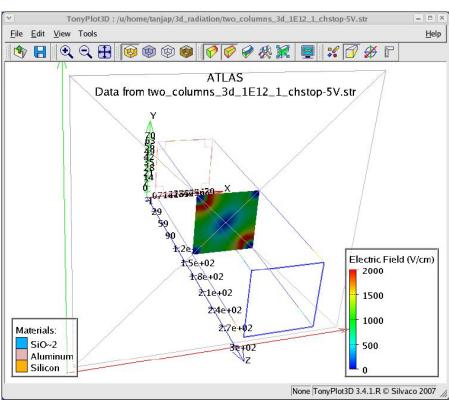


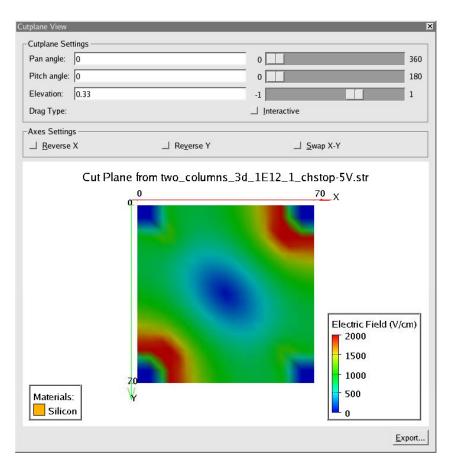


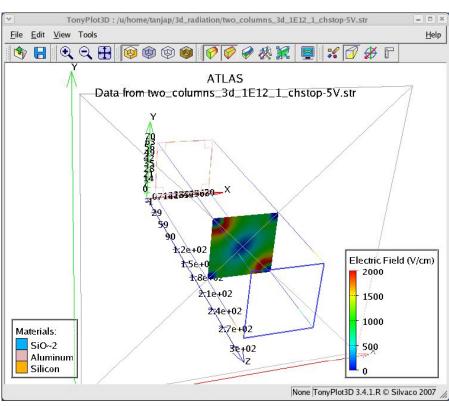


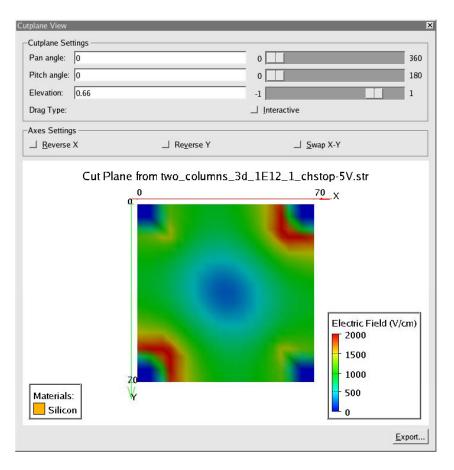


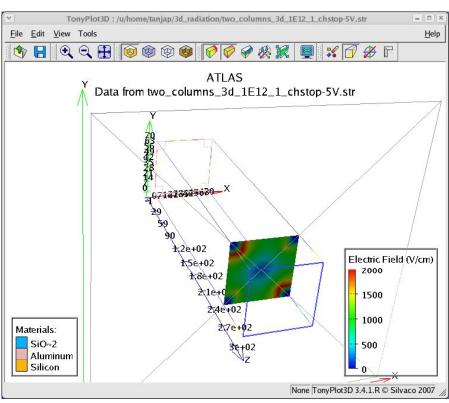


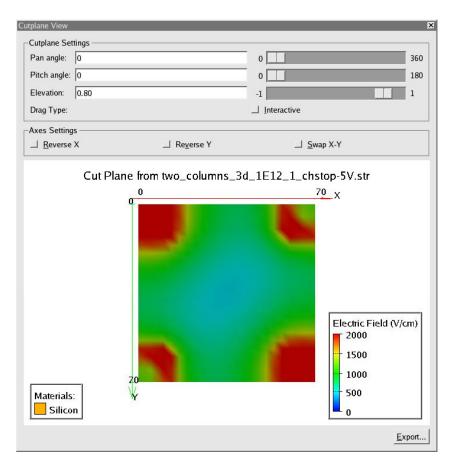


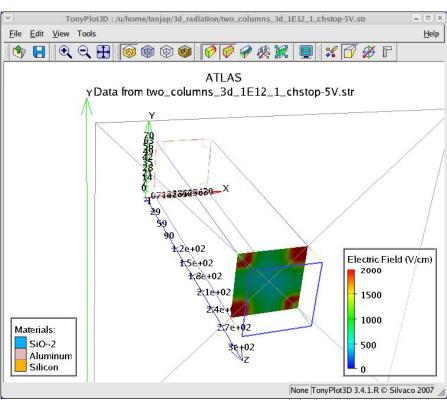


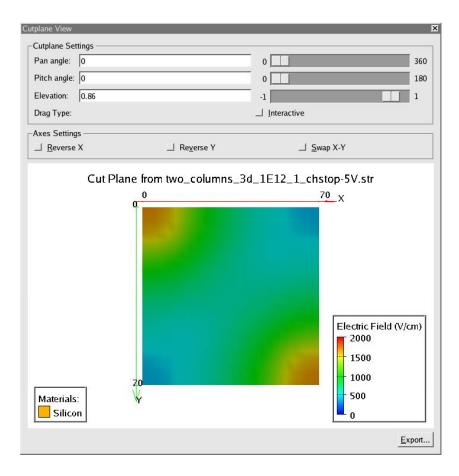


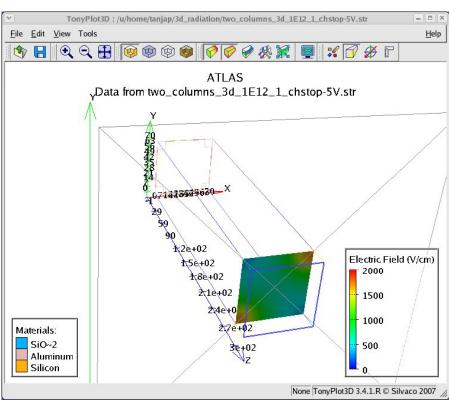


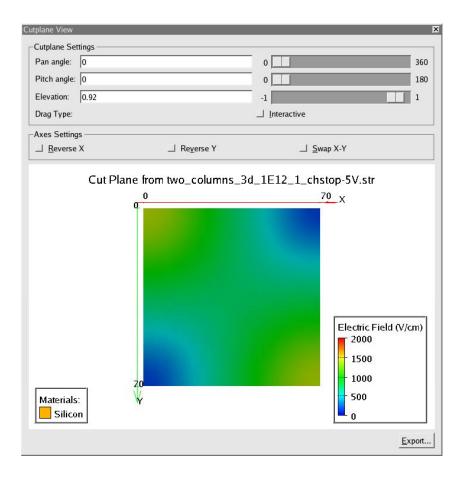


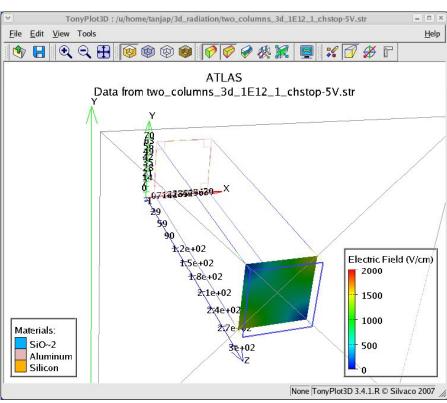


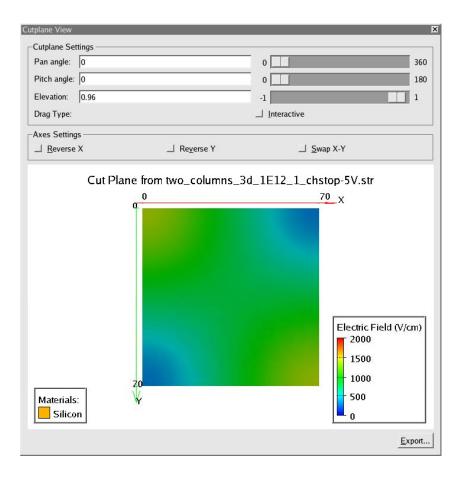


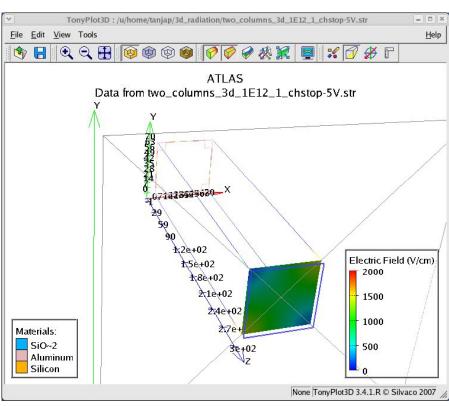


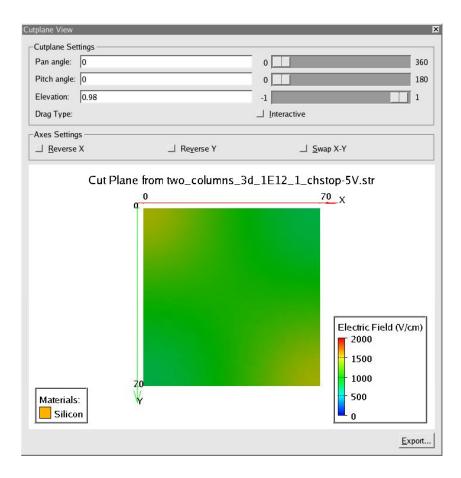


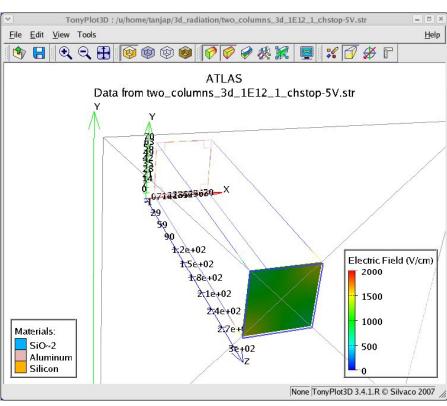


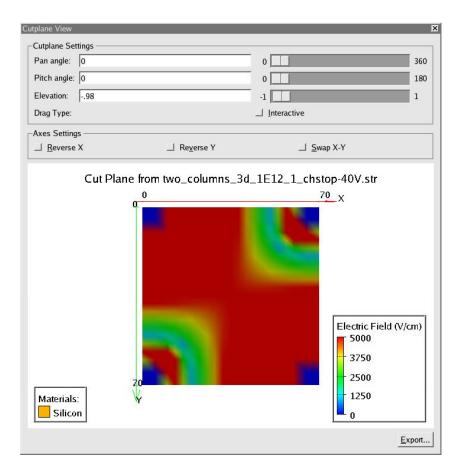


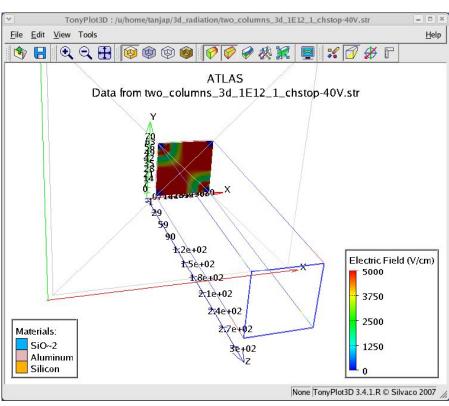


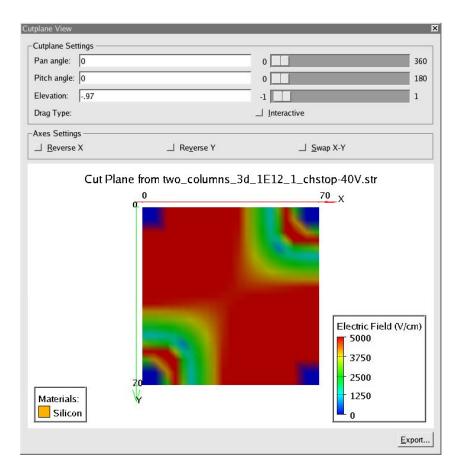


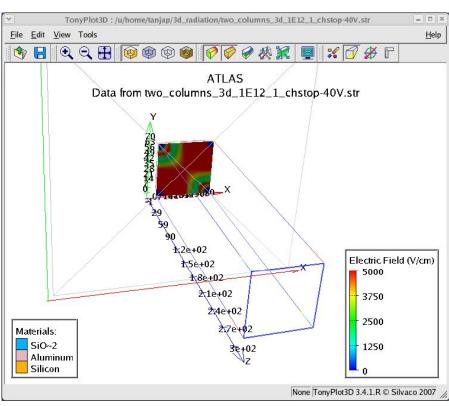


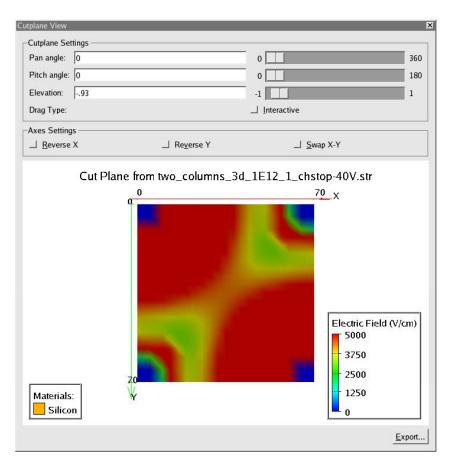


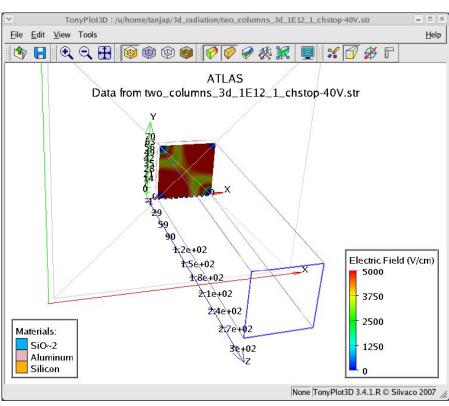


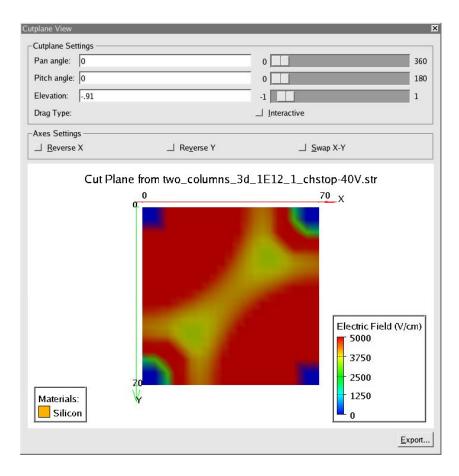


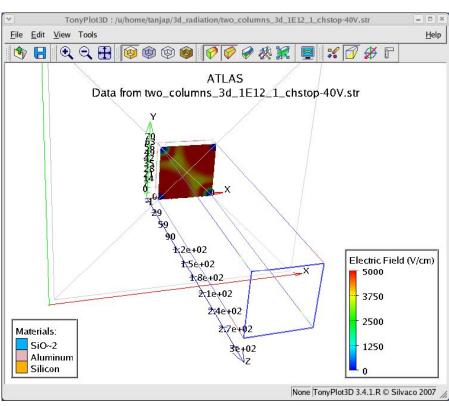


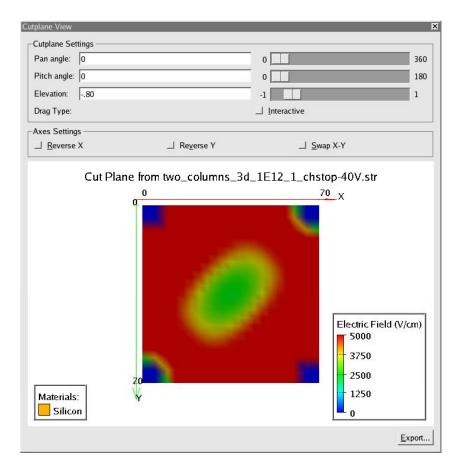


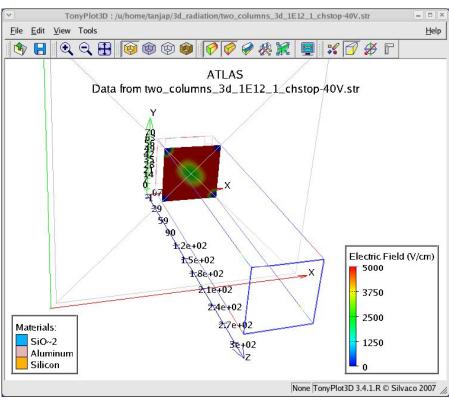


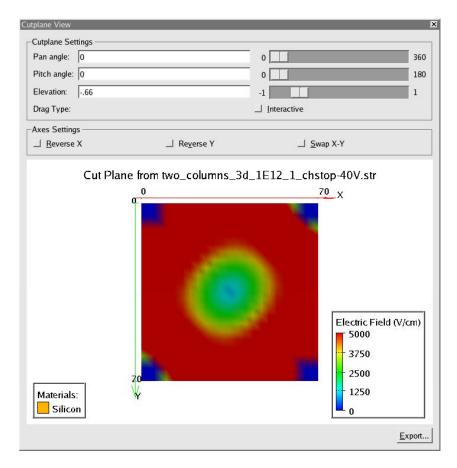


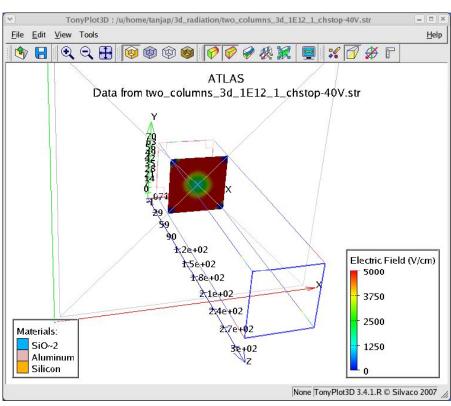


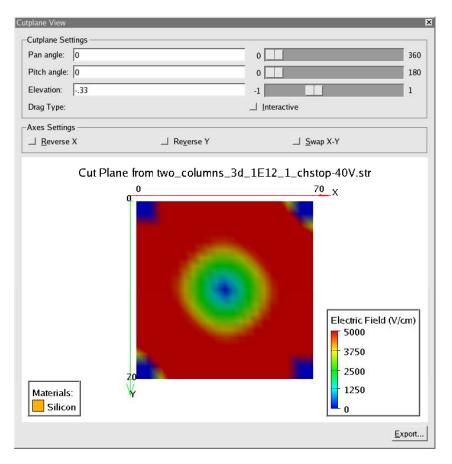


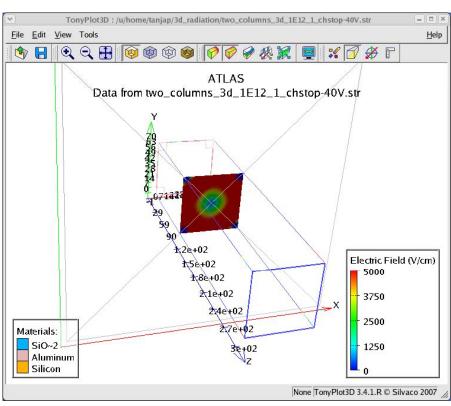


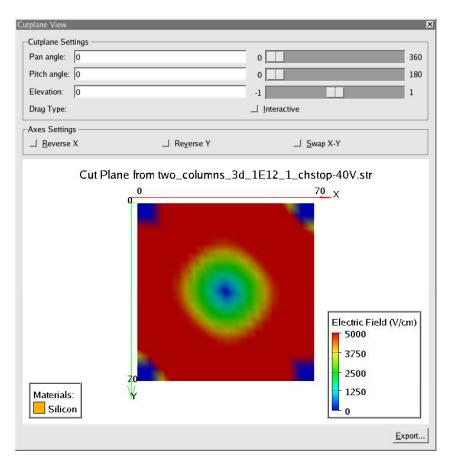


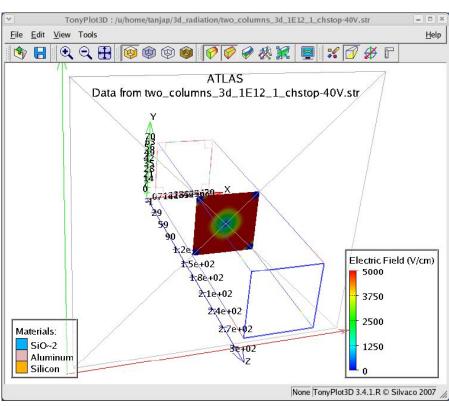


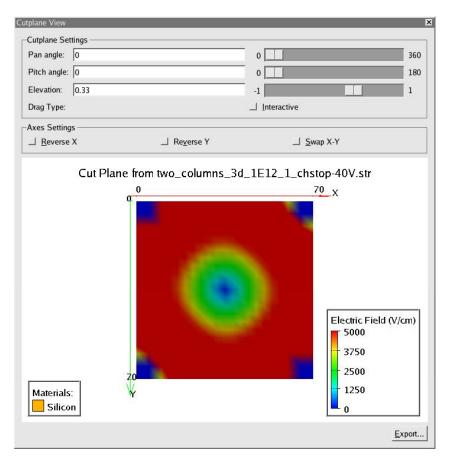


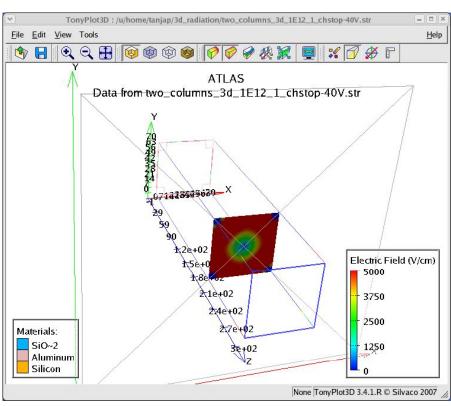


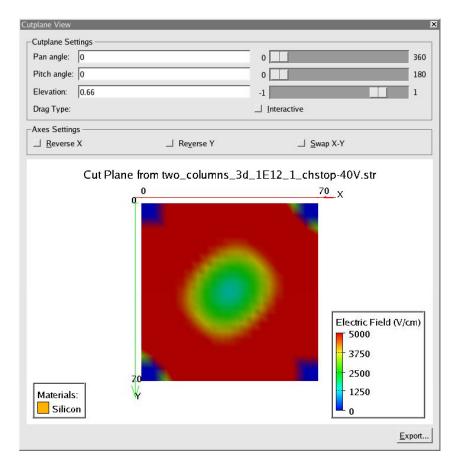


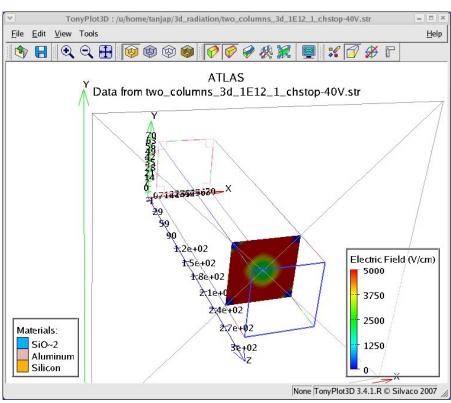


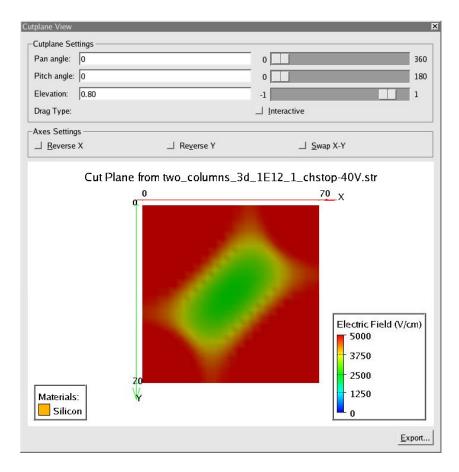


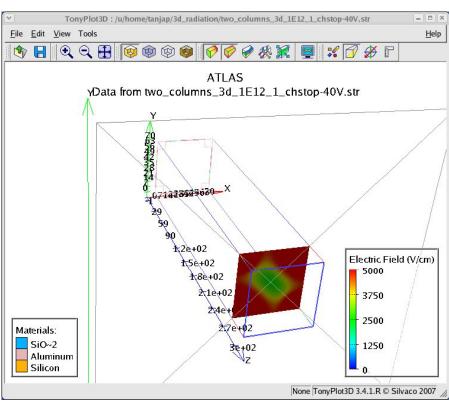


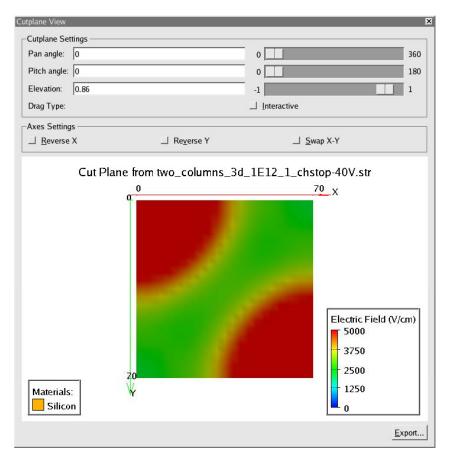


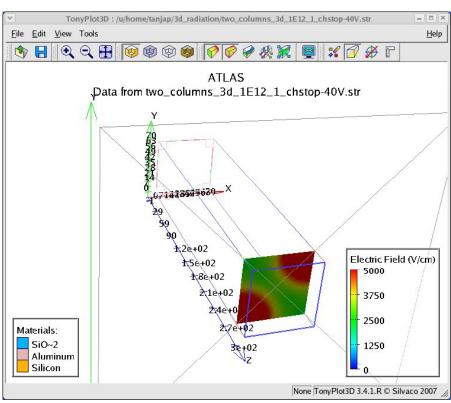


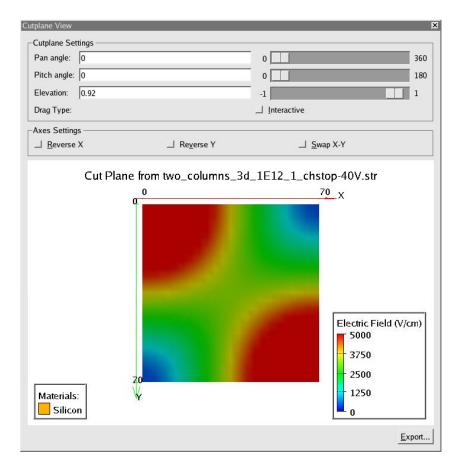


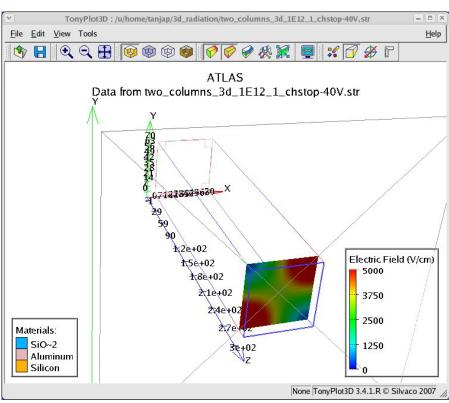


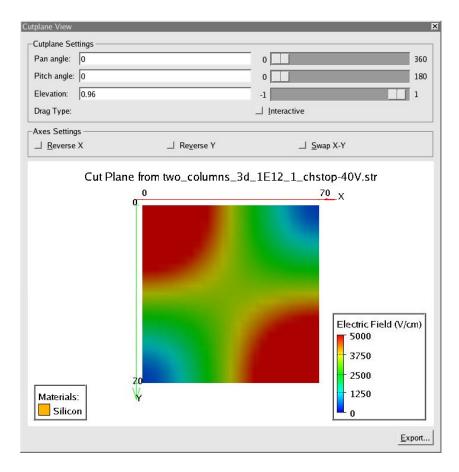


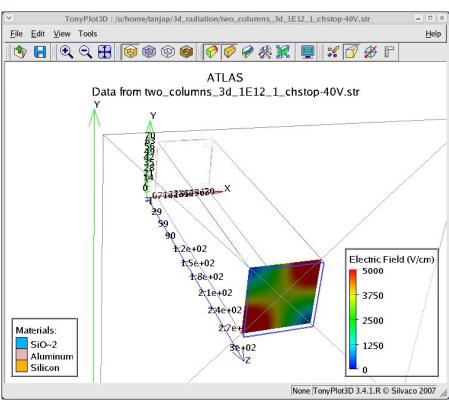


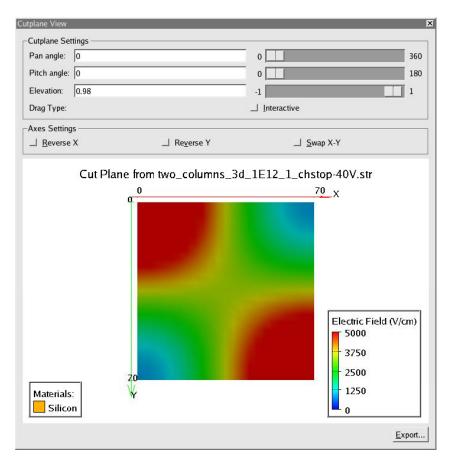


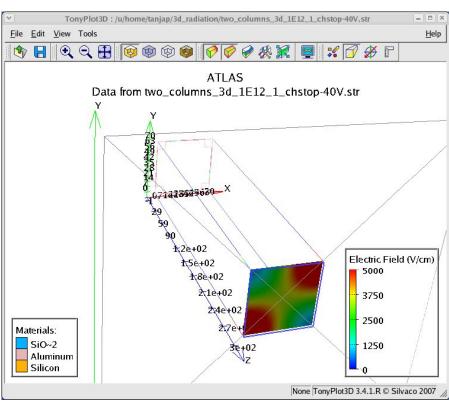






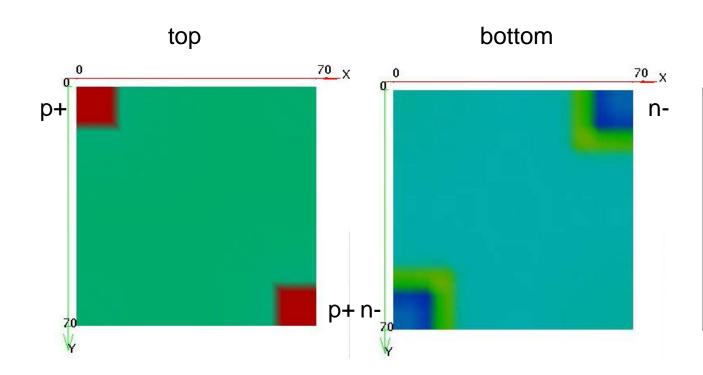


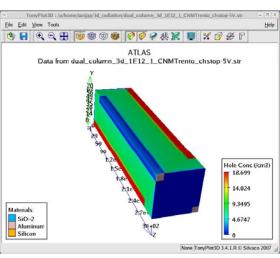




CNM/Trento dual column double-sided 3D detector

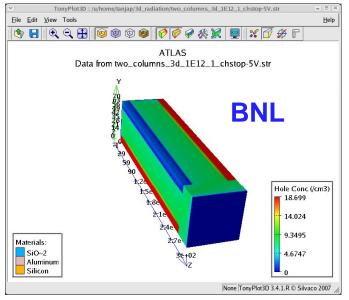
- Under processing at CNM, Barcelona
 RD50 collaborative work (CNM, Glasgow, Valencia,...)
- P-type columns (red) and n-type columns (blue) are placed to the opposite surface, n-type columns are surrounded by p-stops

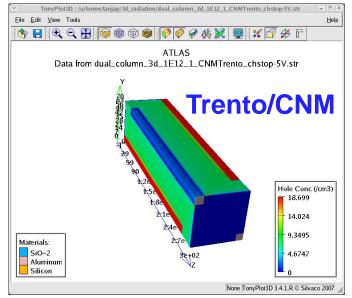


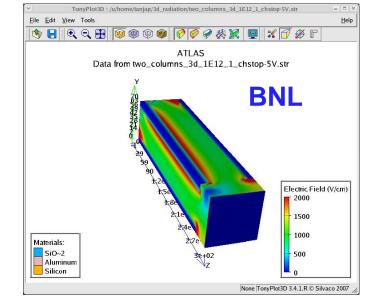


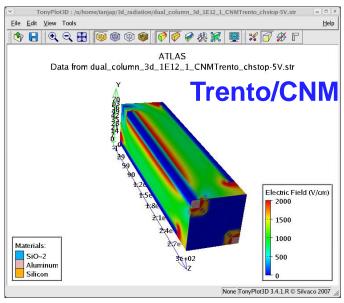
Comparing dual column 3D detectors (5V)

Hole concentration





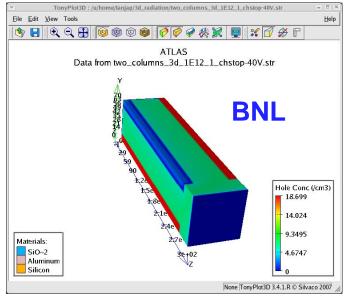


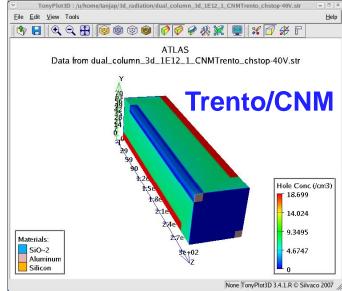


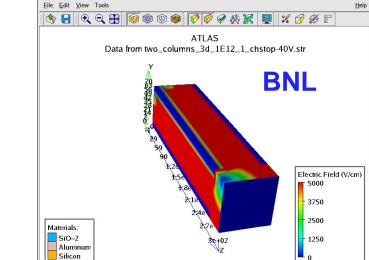
Comparing dual column 3D detectors (40V)

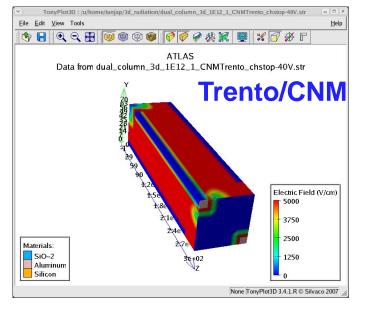
None TonyPlot3D 3.4.1.R © Silvaco 2007

Hole concentration







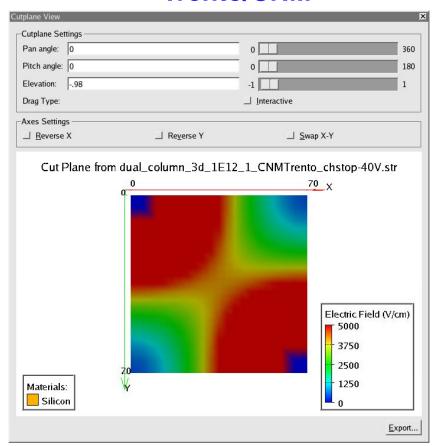


Comparing dual column 3D detectors (40V)



-Cutplane Settings Pan angle: 0 360 Pitch angle: 0 Elevation: -.98 __ Interactive Drag Type: -Axes Settings ☐ Reverse Y Cut Plane from two_columns_3d_1E12_1_chstop-40V.str 70 X Electric Field (V/cm) 5000 3750 2500 1250 Materials: Silicon Export...

Trento/CNM



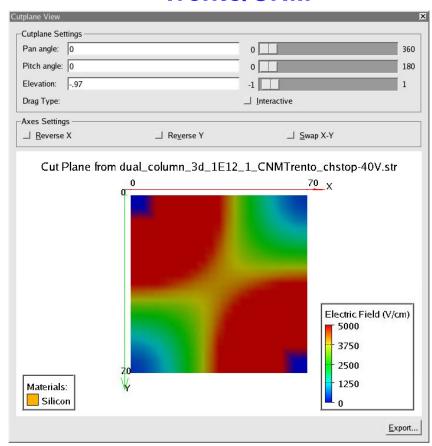
1 µm from the front surface

Comparing dual column 3D detectors (40V)

BNL

-Cutplane Settings Pan angle: 0 Pitch angle: 0 Elevation: -.97 __ Interactive Drag Type: -Axes Settings ☐ Reverse Y Cut Plane from two_columns_3d_1E12_1_chstop-40V.str 70 X Electric Field (V/cm) 5000 3750 2500 1250 Materials: Silicon Export...

Trento/CNM

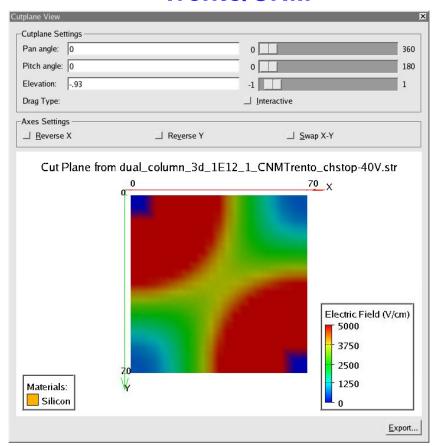


5 µm from the front surface

BNL

-Cutplane Settings Pan angle: 0 360 Pitch angle: 0 Elevation: -.93 __ Interactive Drag Type: -Axes Settings ☐ Reverse Y Cut Plane from two_columns_3d_1E12_1_chstop-40V.str 70 X Electric Field (V/cm) 5000 3750 2500 1250 Materials: Silicon Export...

Trento/CNM

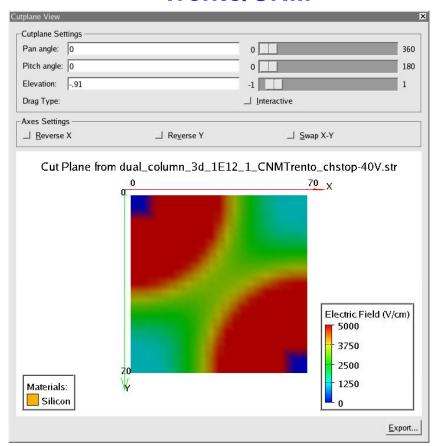


10 µm from the front surface

BNL

-Cutplane Settings Pan angle: 0 Pitch angle: 0 Elevation: -.91 Drag Type: __ Interactive -Axes Settings ☐ Reverse Y Cut Plane from two_columns_3d_1E12_1_chstop-40V.str 70 X Electric Field (V/cm) 5000 3750 2500 1250 Materials: Silicon Export...

Trento/CNM

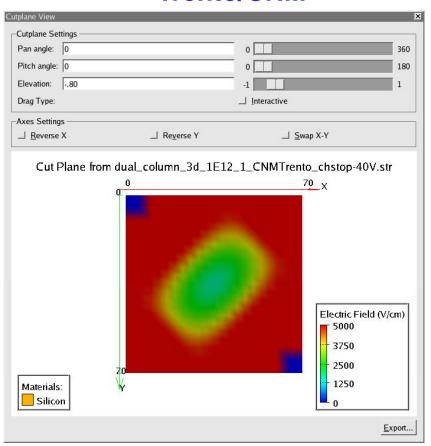


15 µm from the front surface



-Cutplane Settings Pan angle: 0 Pitch angle: 0 Elevation: -.80 __ Interactive Drag Type: -Axes Settings ☐ Reverse Y Cut Plane from two_columns_3d_1E12_1_chstop-40V.str 70 X Electric Field (V/cm) 5000 3750 2500 1250 Materials: Silicon Export...

Trento/CNM

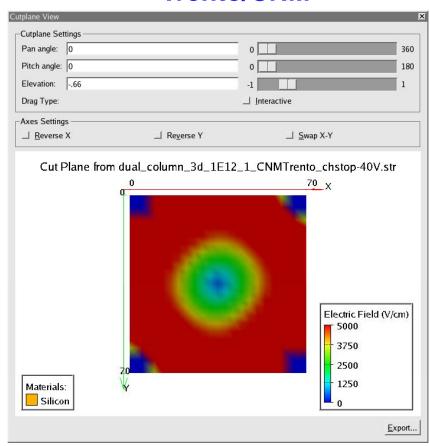


30 µm from the front surface



-Cutplane Settings Pan angle: 0 Pitch angle: 0 Elevation: -.66 __ Interactive Drag Type: -Axes Settings ☐ Reverse Y Cut Plane from two_columns_3d_1E12_1_chstop-40V.str 70 X Electric Field (V/cm) 5000 3750 2500 1250 Materials: Silicon Export...

Trento/CNM

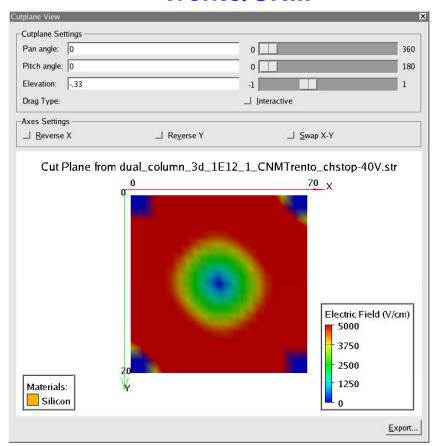


50 µm from the front surface



-Cutplane Settings Pan angle: 0 Pitch angle: 0 Elevation: -.33 __ Interactive Drag Type: -Axes Settings ☐ Reverse Y Cut Plane from two_columns_3d_1E12_1_chstop-40V.str 70 X Electric Field (V/cm) 5000 3750 2500 1250 Materials: Silicon Export...

Trento/CNM

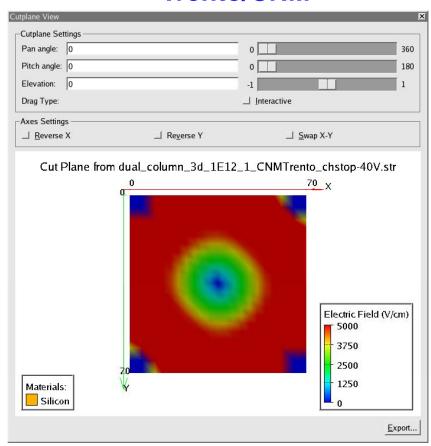


100 µm from the front surface

BNL

-Cutplane Settings Pan angle: 0 Pitch angle: 0 Elevation: 0 __ Interactive Drag Type: -Axes Settings ☐ Reverse Y Cut Plane from two_columns_3d_1E12_1_chstop-40V.str 70 X Electric Field (V/cm) 5000 3750 2500 1250 Materials: Silicon Export...

Trento/CNM

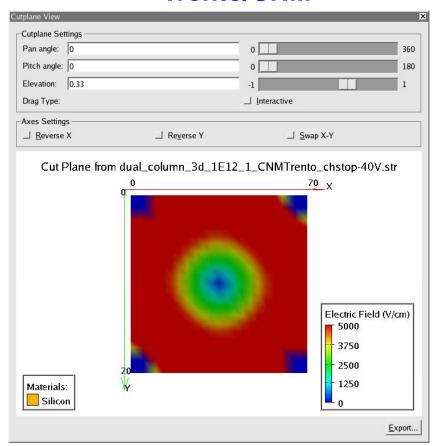


150 µm from the front surface



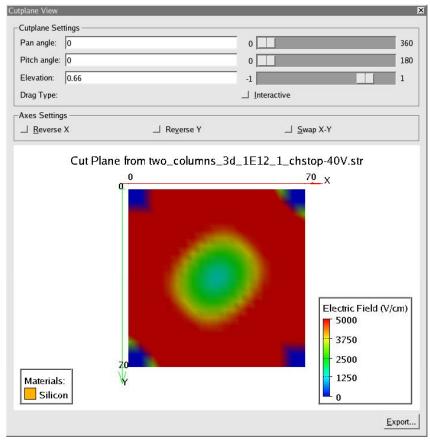
-Cutplane Settings Pan angle: 0 Pitch angle: 0 Elevation: 0.33 __ Interactive Drag Type: -Axes Settings ☐ Reverse Y Cut Plane from two_columns_3d_1E12_1_chstop-40V.str 70 X Electric Field (V/cm) 5000 3750 2500 1250 Materials: Silicon Export...

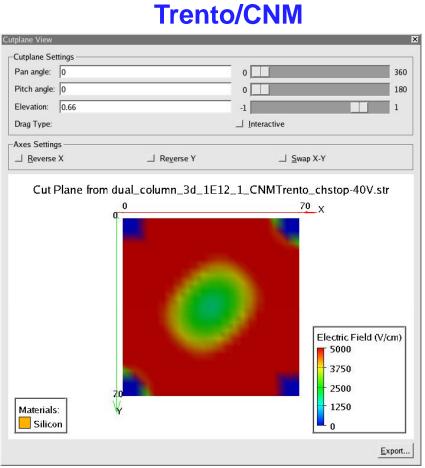
Trento/CNM



200 µm from the front surface





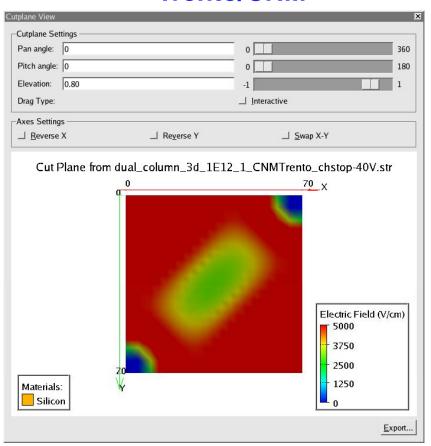


250 µm from the front surface



-Cutplane Settings Pan angle: 0 Pitch angle: 0 Elevation: 0.80 __ Interactive Drag Type: -Axes Settings ☐ Reverse Y Cut Plane from two_columns_3d_1E12_1_chstop-40V.str 70 X Electric Field (V/cm) 5000 3750 2500 1250 Materials: Silicon Export...

Trento/CNM

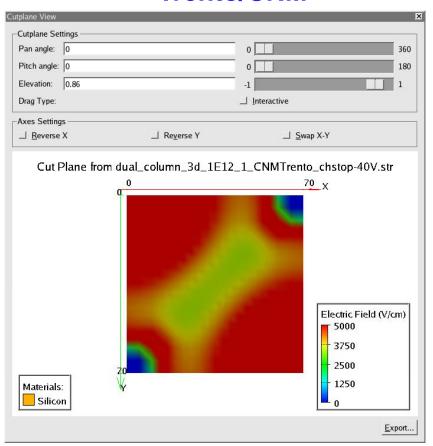


270 µm from the front surface



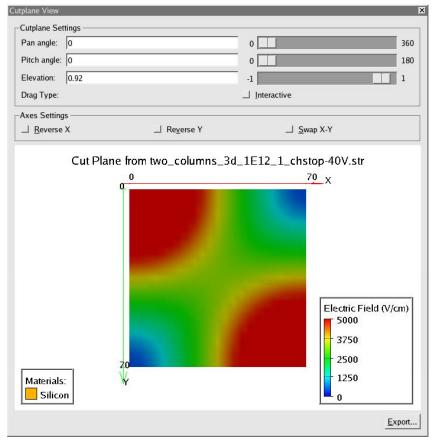
-Cutplane Settings Pan angle: 0 Pitch angle: 0 Elevation: 0.86 __ Interactive Drag Type: -Axes Settings ☐ Reverse Y Cut Plane from two_columns_3d_1E12_1_chstop-40V.str 70 X Electric Field (V/cm) 5000 3750 2500 1250 Materials: Silicon Export...

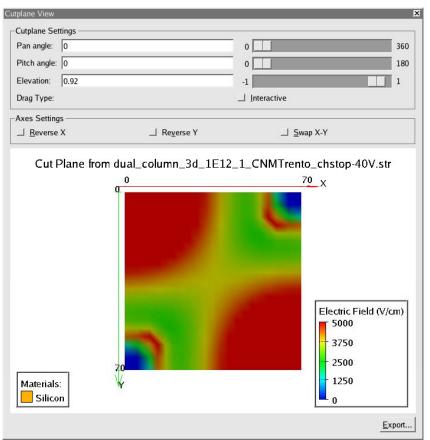
Trento/CNM



280 µm from the front surface

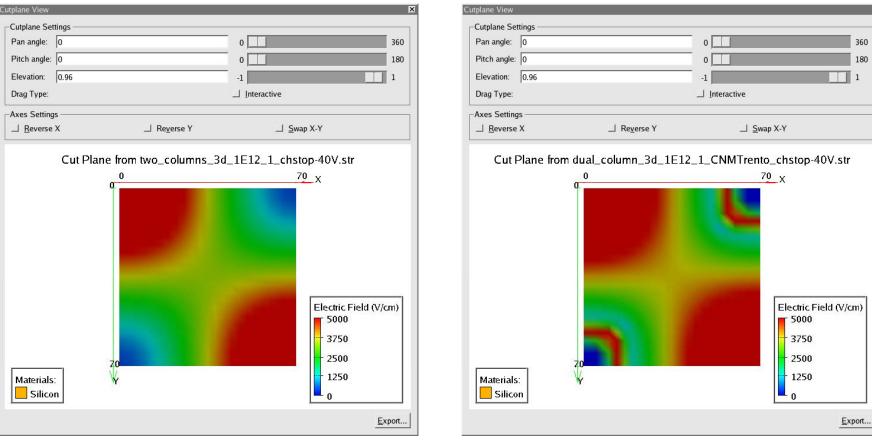
BNL Trento/CNM





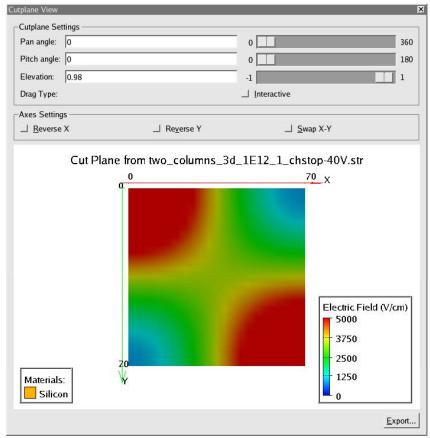
290 µm from the front surface

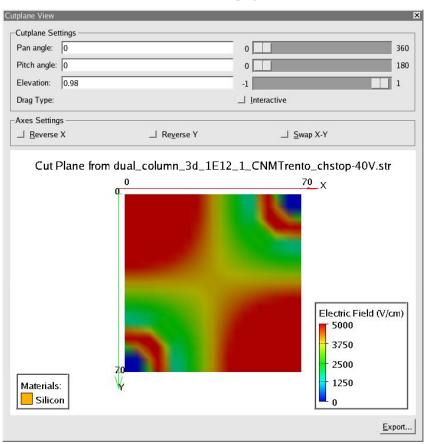




295 µm from the front surface

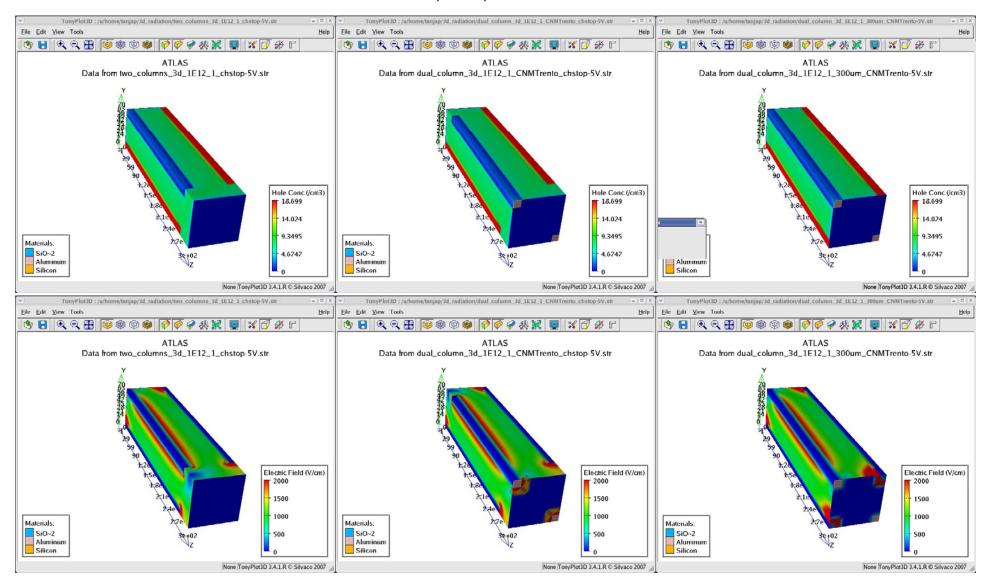






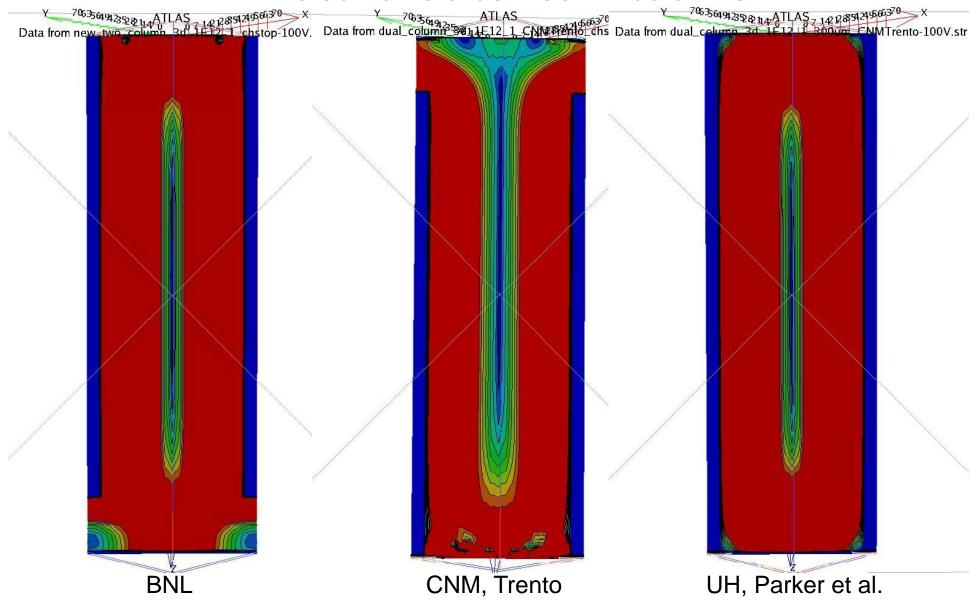
299 µm from the front surface

Dual column 3D detector, 5V, hole concentration and electric field



BNL CNM, Trento UH, Parker et al.

Dual column 3D detector, 100V, electric field between n-columns



Profiles are similar, minor differences on surfaces

Advantages and disadvantages

- 1-column vs. dual column
 - 1-column: one-sided process (BNL: true one-sided process); one-sided access; wafer mechanical strength; more rad-hard than 2d
 - Non-uniform e-field along the column, not super-radiation hard
 - Dual column: better e-field, superradiation hard
 - **Complicated processing**
- BNL 1-column vs. Trento 1-column
 - BNL: true-one-sided process; high e-field on the pixel side; some high e-field can be developed along the junction column at high voltages

- BNL dual-column vs. UH dual-column
 - BNL: true one-sided process; one-sided access; wafer mechanical strength; sensitivity under the columns (reducing the dead volume)
- BNL dual-column vs. Trento/CNM dualcolumn
 - BNL: true-one-sided process
 - Trento/CNM: 2-sided access: separation of two different high bias voltages double-sided process
- E-field profiles are all similar

Structure	E-field profile	Rad- hard	Mechanical integrity	Processing	Accessibility	Sensitivity under the column
Std 3d (UH)	Good	Super	No	Difficult	One-side	No
BNL dual-C	Good	Super	Good	True one- sided	One-side	Some
Trento/CNM dual-C	Good	Super	Good	Double- sided	Two-side	Some
BNL single-C	Low field on the back side	Good	Good	True one- sided	One-side	Some
Trento single-C	Low field on the front and center	Good	Good	One-sided	One-side	Some

Conclusions

- BNL one-sided single column and dual column 3D Si detectors have been simulated in detail and compared to various 3D detector structures.
- Dual column detectors are best in the radiation-hard, but single column detectors are easier to process.
- Disadvantage of these single column detectors is the non-uniform e-field.
- In BNL single column 3D detectors, some high field can be developed along the junction column.